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(54) **PMOS single-poly non-volatile memory structure**

Nichtflüchtige PMOS-Speicheranordnung mit einer einzigen Polysiliziumschicht

Dispositif de mémoire rémanente PMOS à un seul niveau de polysilicium

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- **IBM TECHNICAL DISCLOSURE BULLETIN, vol. 35, no. 5, October 1992, NEW YORK US, pages 339-340, XP000312997 "High-speed, low power/low-voltage P-channel-hot-carrier programming and tunneling erase through silicon-rich oxide"**

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## Description

[0001] The present invention relates to a P-channel non-volatile memory cell having a P+ drain formed in an N-well and a method for operating a P-channel non-volatile memory cell.

[0002] It is desirable, when embedding memory cells into a standard logic process, to do so without changing the single-poly process typically used in the fabrication of the logic circuitry. This desire has led to the development of single-poly memory cells having N+ source and N+ drain regions formed in a P-type substrate and a poly-silicon gate overlying a channel region extending between the P+ source and P+ drain regions. An N-type diffusion region formed in the P-type substrate serves as the control gate and is capacitively coupled to the floating gate via a thin oxide layer, as described in European patent publication 0 044 384 and European patent publication 0 471 131. The oxide layer, has a tunnel window opened in a portion thereof near the N+ drain to facilitate electron tunneling. Since the control gate and floating gate of this single-poly cell form a capacitor in a manner similar to that of the more traditional stacked gate memory cells, the single-poly cell may be programmed, erased, and read in a manner similar to that of the double-poly cell. That is, programming is accomplished by electron tunneling from the floating gate to the substrate, while erasing is realized by electron tunneling from the substrate/drain region to the floating gate.

[0003] The above-described N-channel single-poly memory cell is disadvantageous since it requires high programming and erasing voltages which may be, for instance, as high as 20 V. These high programming and erase voltages limit the extent to which the size of such memory cells may be reduced.

[0004] According to a first aspect of the present invention, there is provided a P-channel non-volatile memory cell having a P+ source and a P+ drain formed in an N-well, a channel extending between said source and said drain, a floating gate overlying said channel, and a first diffusion region formed in said N-well and underlying a first portion of said floating gate, said first diffusion region serving as a control gate of said cell; said memory cell being characterized by a second diffusion region formed in said N-well and underlying a second portion of said floating gate, said second diffusion region serving as an erase gate of said cell; and a third diffusion region formed in said N-well, wherein said control gate is formed within said third diffusion region, and wherein said third diffusion region is of a conductivity type opposite that of said control gate and of said well to electronically isolate said control gate from said N-well.

[0005] In a preferred embodiment, the memory cell further comprises a fourth diffusion region formed in said N-well, said fourth diffusion region being of a conductivity type opposite that of said erase gate, wherein said erase gate is formed within said fourth diffusion region whereby said fourth diffusion region electronically isolates said erase gate from said N-well.

[0006] According to a second aspect of the present invention, there is provided a method of operating a P-channel non-volatile memory cell, said cell comprising a P+ source and a P+ drain formed in an N-well, a channel extending between said source and said drain, a floating gate overlying said channel, a first diffusion region formed in said N-well and underlying a first portion of said floating gate, said diffusion region serving as a control gate of said cell, and a second diffusion region formed in said N-well and underlying a second portion of said floating gate, said second diffusion region serving as an erase gate of said cell, and a third diffusion region formed in said N-well, wherein said control gate is formed within said third diffusion region and wherein said third diffusion region is of a conductivity type opposed to that of said control gate and of said well, said method being characterized by tunneling electrons from said drain to said floating gate and hot injecting electrons from a portion of said channel proximate of said drain to said floating gate to program said memory cell, said control gate being electrically isolated from said N-well.

[0007] The invention will now be described by way of example, with reference to the accompany drawings, in which Figures 1-20 and 22d are for reference purposes and Figures 21-22c, 23, 24 and 25 are according to the invention. In the figures:

Figure 1 is a top view of a PMOS single-poly flash cell;  
 Figure 2 is a cross-sectional view of the cell of Figure 1 taken along line A-A;  
 Figures 3A and 3B are cross-sectional views of the cell of Figure 1 taken along line B-B;  
 Figure 4 is a cross-sectional view of the cell of Figure 1 taken along line C-C;  
 Figure 5 is a top view of a PMOS single-poly EEPROM cell;  
 Figure 6 is a cross-sectional view of the cell of Figure 5 taken along line E-E;  
 Figure 7 is a cross-sectional view of the cell of Figure 5 taken along line F-F;  
 Figure 8 is a top view of a PMOS single-poly memory cell;  
 Figure 9 is a cross-sectional view of the cell of Figure 8 taken along line G-G;  
 Figure 10 is a cross-sectional view of the cell of Figure 8 taken along line H-H;  
 Figure 11 is a cross-sectional view of the cell of Figure 8 taken along line I-I;  
 Figure 12 is a cross-sectional view of yet another memory cell;  
 Figures 13 and 14 illustrated the fabrication of a P-channel single-poly memory cell;  
 Figure 15 is a top view of a PMOS single-poly memory device having an erase gate;

Figure 16 is a cross-sectional view of the device of Figure 15 taken along line AA-AA;  
 Figure 17 is a cross-sectional view of the device of Figure 15 taken along line BB-BB;  
 Figure 18 is a cross-sectional view of the device of Figure 15 taken along line CC-CC;  
 Figure 19 is a cross-sectional view of the device of Figure 15 taken along line DD-DD;  
 Figure 20 is a cross-sectional view of the device of Figure 15 taken along line EE-EE;  
 Figure 21 is a top view of a PMOS single-poly non-volatile memory cell in accordance with the present invention;  
 Figure 22A is a cross-sectional view of the cell of Figure 21 taken along line A-A;  
 Figures 22B-2C are cross-sectional view of cells in accordance with other embodiments of the present invention;  
 and  
 Figure 22D is a cross-sectional view of a cell described for reference purposes;  
 Figure 23 is a cross-sectional view of the cell of Figure 21 taken along line B-B;  
 Figure 24 is a cross sectional view of a portion of a PMOS single-poly cell in accordance with another embodiment of the present invention; and  
 Figure 25 is a schematic diagram of a memory array structure employing PMOS single-poly cells of the present invention.

[0008] Referring to Figures 1-4, a P-channel single-poly memory cell 10 is formed in an N-well 12 provided within a P-type substrate 14 and includes a P-channel storage transistor 16 and a P-channel select transistor 18. P+ diffusion region 20 serves as the source of storage transistor 16, P+ diffusion region 22 serves as both the drain of storage transistor 16 and the source of select transistor 18, and P+ diffusion region 24, which is coupled to a bit line BL, serves as the drain of select transistor 24. Poly-silicon gates 26 and 28 serve as the floating gate and select gate, respectively, of cell 10.

[0009] A P-type buried diffusion layer 36 serves as the control gate of cell 10. A contact region 38 is opened in floating gate 26 and in a layer of oxide 40 interposed between floating gate 26 and control gate 36 to enable electrical contact with buried control gate 36. Tunnel oxide layer 34, which is preferably 80-130 Å thick, may extend over channel 30 and substantial portions of source 20 and drain 22. A layer of oxide 40 approximately 80-350 Å thick is provided between floating gate 26 and P diffusion region 36. It is also to be noted that unlike conventional N-channel single-poly EEPROM cells, it is not necessary to open a tunnel window in tunnel oxide layer 34. Application of a bias voltage to control gate 36 enhances a channel 30 extending between source 20 and drain 22 of storage transistor 16, and the application of a bias voltage to select gate 28 enhances a channel 32 extending between source 22 and drain 24 of select transistor 18.

[0010] Together, floating gate 26 and control gate 36 form an MOS capacitor in a manner similar to that of conventional N-channel EEPROM cells. When floating gate 26 is unchanged, cell 10 has a threshold voltage  $V_t$  of approximately -4.5V.

[0011] The operation of cell 10 is as follows. To program cell 10, bit line BL and select gate 28 are grounded while source 20 and N-well 12 are held at approximately 8 V. Approximately 8.5 V is applied to control gate 36. Positively charged holes from P+ source 20 are attracted to the less positive voltage on P+ drain 22. These holes collide with electrons in a depletion layer proximate drain 22. High energy electrons generated from the resultant impact ionization are attracted by the positive voltage on floating gate 26 (approximately 7.5 V is capacitively coupled thereto via control gate 36, source 20, channel region 30, and drain 22) and are thus injected from the drain depletion layer into floating gate 26. The resultant negative charge on floating gate 22 depletes channel region 12. In some embodiments, storage transistor 16 has in its programmed state a threshold voltage  $V_t$  equal to approximately 1 V. It is preferred that a current limiting device (not shown) is coupled to a bit line BL to prevent programming currents from exceeding approximately 100  $\mu$ A, thereby limiting power consumption during programming.

[0012] Cell 10 is erased by applying approximately 18 V to bit line BL, P+ source 20, and N-well 12 while grounding select gate 26 and control gate 36. Electrons tunnel from floating gate 26 through the entire length of tunneling oxide layer 34 into channel 30, source 20, and drain 22, thereby returning the threshold voltage of storage transistor 16 to its normal erased state value of approximately -4 V. Note that electrons will tunnel from floating gate 26, and thereby erase cell 10, only if the voltage on drain 22 is or exceeds approximately 18 V.

[0013] Alternatively, cell 10 may be erased by applying approximately 8 V to bit line BL, P+ source 20, and N-well 12 while grounding select gate 26 and applying approximately -10 V to control gate 36. The application of these erase voltages, which results in an erasing of cell 10 in a manner identical to that described earlier, advantageously requires lower erase voltages.

[0014] Where it is desired to read cell 10, a read voltage of approximately ( $V_{cc} - 2V$ ) is applied to control gate 36 and  $V_{cc}$  is applied to P+ source 20 and to N-well 12. Select gate 26 is grounded. A voltage less than  $V_{cc}$  is applied to P+ drain 16 via bit line BL. Cell 10 will conduct channel current only if cell 10 is programmed, i.e., only if there is negative charge stored in floating gate 26. Thus, since a read current flows through cell 10 when floating gate 26 is negatively charged, a programmed cell 10 does not suffer from read disturb problems characteristic of conventional N-channel EEPROM cells. Further, when cell 10 is in an erased state, the voltage on floating gate 26 is always less than the

voltage on drain 22. In this manner, cell 10 does not exhibit read disturb problems when in an erased state.

**[0015]** Acceptable ranges for the above-described reading, erasing, and programming bias conditions for cell 10 are provided below in Table 1.

Table 1

Electrical bias conditions					
Mode	Bit Line	Select Gate	Source	N-well	Control Gate
Program	0V	0V	5-15V	5-15V	5-15V
Erase (option 1)	3-15V	0V	3-15V	3-15V	-3 to -15V
Erase (option 2)	15-22V	0V	15-22V	15-22V	0V
Read	less than V <sub>cc</sub>	0V	V <sub>cc</sub>	V <sub>cc</sub>	0 to V <sub>cc</sub>

**[0016]** The above-described operation of cell 10 utilizes PMOS characteristics to achieve advantages over conventional N-channel single-poly semiconductor memory cells. The characteristic gate current for P-channel devices is approximately 50 times that of N-channel devices. Thus, unlike conventional NMOS EEPROM cells which typically require approximately a 0.5 milli-amp programming current to charge the floating gate, cell 10 requires a programming current of only a few micro-Amps. Requiring a programming current more than one order of magnitude smaller than that of conventional NMOS non-volatile memory cells (e.g., EPROMs, EEPROMs, and Flash) not only allows for a reduction in power consumption during programming but also allows for page writing, i.e., to simultaneously write to numerous ones of cells 10 in a row of an associated memory array (not shown).

**[0017]** It is known that the channel of conventional NMOS non-volatile memory cells must be of a sufficient length to tolerate the typically high reverse bias voltage across the P-well/N<sup>+</sup> drain junction (as well as the resultant high electric field) required during programming and erasing via electron tunneling. As a result, it is difficult to further reduce the size of such conventional non-volatile cells without incurring destructive junction stress. Since, however, the operation of cell 10 neither requires nor utilizes a high voltage bias across its N-well/P<sup>+</sup> drain junction during programming and erasing (see Table 1), the channel length of cell 10 is not so limited. Indeed, this feature allows cell 10 to be fabricated using 0.18  $\mu\text{m}$  technology, thereby resulting in cell 10 being of a smaller size than conventional N-channel single-poly cells. For instance, while cell 10 is only about 25  $\mu\text{m}^2$  using 0.5  $\mu\text{m}$  technology, conventional N-channel single-poly cells are typically on the order of 160  $\mu\text{m}^2$  using 0.5  $\mu\text{m}$  technology. Further, eliminating such high junction biases during erasing advantageously results in a more durable and reliable memory cell.

**[0018]** It is also known that as the channel length of an NMOS transistor falls below approximately 0.7  $\mu\text{m}$ , electron mobility saturates. In PMOS devices, however, hole mobility continues to increase as the channel length decreases below 0.7  $\mu\text{m}$  and becomes comparable to electron mobility as the channel length is further decreased. Accordingly, minimizing the channel lengths of storage transistor 16 and select transistor 18 advantageously results in a hole mobility comparable to electron mobility, thereby increasing the speed with which cell 10 may be read. Further, note that when programmed cell 10 is in deep depletion. This allows for a higher read current and thus for faster read speeds.

**[0019]** As described above and shown in Table 1, PMOS single-poly cell 10 requires only approximately 8.5 V for programming and erasing operations, as compared to the 20 V or more required for programming and erasing conventional NMOS single-poly memory cells, and is thus more readily adaptable to the low voltage operation of a standard logic process.

**[0020]** Cell 10 is also capable of storing numerous bits of binary data by programming storage transistor 16 to one of many different threshold voltage  $V_t$  levels, where the  $V_t$  levels depend on, and are thus determined by, the voltage applied to control gate 36. In such multi-level threshold voltage applications, where it is necessary to accurately measure the threshold voltage  $V_t$  of storage transistor 16, drain 24 of select transistor 18 is coupled to  $V_{cc}$  through a high impedance resistor R and to a voltage sensing circuit 35, as shown in Figure 3B. Sensing circuit 35 allows for accurate determination of the threshold voltage  $V_t$ , and thus the multiple-level data stored in cell 10.

**[0021]** In such multi-level applications, cell 10 has in its natural state a  $V_t$  of approximately -6 V and has in its fully charged state a threshold voltage  $V_t$  of approximately 9 V. Using a range of voltage from 5 V to 15 V as the program voltage  $V_p$  applied to control gate 36 during programming, the threshold voltage  $V_t$  of storage transistor may be set between approximately -1 V and 9 V. Where  $V_{cc}$  is approximately 5 V, the range of bit line BL voltages produced in response to varying the threshold voltage  $V_t$  is approximately 1 to 5 V, thereby resulting in a 4 V range. Since the threshold voltage  $V_t$  of storage transistor 16 may be programmed in 4 mV increments, 1000 levels of programming are possible with cell 10. Acceptable ranges for bias conditions during programming, reading, and erasing cell 10 for multi-level applications are listed below in Table 2.

Table 2

Electrical bias conditions					
Mode	Bit Line	Select Gate	Source	N-well	Control Gate
Program (option 1)	0V	0V	5-15V	5-15V	desired $V_p$ , i.e. (5-15V)
Program (option 2)	0V	0V	5-15V	5-15V	ramp up to desired $V_p$
Erase (option 1)	3-15V	0V	3-15V	3-15V	-3 to -15V
Erase (option 2)	15-22V	0V	15-22V	15-22V	0V
Read (option 1)	less than $V_{cc}$	0V	$V_{cc}$	$V_{cc}$	0 to $V_{cc}$
Read (option 2)	pre-charge to $V_{cc}$	0V	0V	$V_{cc}$	0V

[0022] In other alternatives, the structure of cell 10 may be incorporated into a larger PMOS single-poly EEPROM cell 50. Referring to Figures 5-7 (note that the cross-sectional view taken along line D-D is identical to that shown in Figure 2 and is thus not again shown), cell 50 is shown formed in N-well 12 and includes a source select transistor 52 on the source side of cell 10. Those components common to cells 10 and 50 are appropriately labelled with the same numerals. P+ diffusion regions 54 and 20 serve as the source and drain, respectively, of select transistor 52. A polysilicon gate 56 controls an underlying channel region 58. The programming, erasing, and reading operations of cell 50 are nearly identical to that described above with respect to cell 10 and will thus not be discussed in detail here. Acceptable ranges for the bias conditions for programming, erasing, and reading are listed below in Table 3. The addition of source select transistor 52 to cell 10 results in an EEPROM cell 50 that is both bit-to-bit programmable and bit-to-bit erasable. In this manner, erasing flexibility is increased.

Table 3

	Bit line	Drain select gate	Source select gate	Source	N-well	Cell control gate
Program	0V	0V	*	5V-15V	5V-15V	5-15V
Erase (option 1)	3V-15V	0V	3V-15V	3V-15V	3V-15V	-3V to -15V
Erase (option 2)	15V-22V	0V	15V-22V	15V-22V	15V-22V	0V
Read	less than $V_{cc}$	0V	0V	$V_{cc}$	$V_{cc}$	0V to $V_{cc}$

\* 0 to (source voltage - 1V)

[0023] In a manner similar to that described above with respect to cell 10, cell 50 may be used in multi-level threshold voltage applications. In such applications, drain 24 of drain select transistor 18 is coupled to  $V_{cc}$  through a high impedance resistor R (not shown) and to a voltage sensing circuit (not shown). The sensing circuit allows for accurate determination of the threshold voltage  $V_t$  and thus the multiple-level data stored in cell 50. Acceptable ranges for bias conditions during programming, reading, and erasing cell 50 for multi-level applications are listed below in Table 4.

Table 4

	Bit line	Drain select gate	Source select gate	Source	N-well	Cell control gate
Program (option 1)	$V_p$	0V	3V-15V	3V-15V	3V-15V	-3V to -15V
Program (option 2)	$V_p$	0V	15V-22V	15V-22V	15V-22V	0V
Erase	0V	0V	*	5V-15V	5V-15V	5V-15V
Read (option 1)	less than $V_{cc}$	0V	0V	$V_{cc}$	$V_{cc}$	0 to $V_{cc}$
Read (option 2)	pre-charge to $V_{cc}$	0V	0V	0V	$V_{cc}$	0V

\* 0 to (source voltage - 1V)

[0024] In yet another alternative, cell 60 includes storage transistor 16 which is coupled directly to bit line BL and source select transistor 52 which is coupled to source 20 of storage transistor 16, as shown in Figures 8-11, where those components common to cells 10, 50, and 60 are appropriately labelled with the same numerals. Note that drain 22 of storage transistor 16 may be coupled to  $V_{cc}$  via high impedance resistor R and also to voltage sensing circuit 35 to enable accurate determination of the programmed threshold voltage  $V_t$  of storage transistor 16. Cell 60 is of a smaller size than cell 50 and allows for column, i.e. sector, erasing. The operation of cell 60 is similar to that described above with respect to cell 50. Acceptable bias condition ranges for programming, erasing, and reading cell 60 are listed below in Table 5.

Table 5

	Bit line	Source select gate	Source	N-well	Cell control gate
Program (option 1)	0V	0V	5V-15V	5V-15V	5V to -15V
Program (option 2)	0V	0V	5V-15V	5V-15V	0V ramped up to 5V-15V
Erase (option 1)	3V-15V	0V	3V-15V	3V-15V	-3V to -15V
Read (option 2)	15V-22V	0V	15V-22V	15V-22V	0V
Read	less than $V_{cc}$	0V	$V_{cc}$	$V_{cc}$	0V to $V_{cc}$
* 0 to (source voltage - 1V)					

[0025] In a manner similar to that described above with respect to cell 10, cell 60 may be used in multi-level threshold voltage applications. Acceptable ranges for bias conditions during programming, reading, and erasing cell 60 for multi-level applications are listed below in Table 6.

Table 6

Electrical bias conditions					
Mode	Bit Line	Select Gate	Source	N-well	Control Gate
Program (option 1)	0V	0V	5-15V	5-15V	desired $V_p$ , i.e., (5-15V)
Program (option 2)	0V	0V	5-15V	5-15V	ramp up to desired $V_p$
Erase (option 1)	3-15V	0V	3-15V	3-15V	-3 to -15V
Erase (option 2)	15-22V	0V	15-22V	15-22V	0V
Read (option 1)	less than $V_{cc}$	0V	$V_{cc}$	$V_{cc}$	0 to $V_{cc}$
Read (option 2)	pre-charge to $V_{cc}$	0V	0V	$V_{cc}$	0V

[0026] The above-described devices in which single-poly transistor 16 is used as the storage cell suffer from a common drawback. Referring to Figure 2, the P/N junction formed by control gate 36 and N-well 12 must remain reverse biased in order to prevent a large and undesirable current flow from control gate 36 to N-well 12. Accordingly, the voltage applied to control gate 36 should never exceed the voltage of N-well 12 by more than approximately 0.6 V. As a result, the voltage coupled to floating gate 26 via control gate 36 is limited by the amount of voltage applied to N-well 12. Thereby unnecessarily restricting the performance of transistor 16.

[0027] In another form of memory cell, a single-poly storage transistor 70 is provided the performance of which is not so restricted. Referring now to Figure 12, note that storage transistor 70 is identical to storage transistor 16 in every respect except for the structure of buried control gate 74 the operation and advantages of which will be described below. Accordingly, all components common to transistor 70 (Figure 12) and transistor 16 (Figures 1-4) are appropriately labelled with same numerals.

[0028] Transistor 70 has a P-type diffusion region 72 within N-well 12. An N-type diffusion region 74 is formed within P-type diffusion region 72. N-type diffusion region 74 serves as the control gate for transistor 70, while P-type diffusion region 72 provides electrical isolation between control gate 74 and N-well 12. N-type control gate 74 may be electrically coupled to a contact in the same manner as is control gate 36 of cell 10 (described above with respect to Figures 1-4). Since control gate 74 is an N-type diffusion region and is formed within P-type diffusion region 72, the voltage on control gate 74 may exceed the voltage of N-well 12 without causing an undesirable current flow from control gate 74 to N-well 12. The elimination of such a restriction on the voltage of control gate 74 eliminates the need to maintain N-well 12 at high potentials during programming operations and, thus, allows transistor 70 to go even further into depletion

when programmed. As a result, transistor 70 exhibits a higher read current than does transistor 16.

[0029] \* Storage transistor 70 may replace transistor 16 in any of the above-described memory cells 10, 50, and 60 to allow for faster access times. Tables 7, 8, and 9 list acceptable bias conditions for the programming, erasing, and reading of cells 10, 50, and 60, respectively, when employing transistor 70 as the storage element (as opposed to employing transistor 16).

Table 7

Electrical bias conditions					
Mode	Bit Line	Select Gate	Source	N-well	Control Gate
Program (option 1)	0V	0V	5-15V	5-15V	5-17V
Program (option 2)	0V	0V	5-15V	5-15V	ramp up to between 5-17V from 0V
Erase (option 1)	3-15V	0V	3-15V	3-15V	-3 to -15V
Erase (option 2)	15-22V	0V	15-22V	15-22V	0V
Read	less than Vcc	0V	Vcc	Vcc	0 to Vcc

Table 8

	Bit line	Drain select gate	Source select gate	Source	N-well	Cell control gate
Program	0V	0V	*	5V-15V	5V-15V	5-17V
Erase (option 1)	3V-15V	0V	3V-15V	3V-15V	3V-15V	-3V to -15V
Erase (option 2)	15V-22V	0V	15V-22V	15V-22V	15V-22V	0V
Read	less than Vcc	0V	0V	Vcc	Vcc	0V to Vcc

\* 0 to (source voltage - 1V)

Table 9

	Bit line	Source Select Gate	Source	N-well	Cell control gate
Program(option 1)	0V	0V	5V-15V	5V-15V	5V-17V
Program (option 2)	0V	0V	5V-15V	5V-15V	ramp from 0V up to between 5V-17V
Erase (option 1)	3V-15V	0V	3V-15V	3V-15V	-3 to -15V
Erase (option 2)	15V-22V	0V	15V-22V	15V-22V	0V
Read	less than Vcc	0V	Vcc	Vcc	0V to Vcc
* 0 to (source voltage - 1V)					

[0030] Further, those forms of cells 10, 50, and 60 which employ as storage elements transistor 70 are also capable of multi-level threshold voltage applications, the operation of which is identical to that described above. Acceptable bias condition ranges for the programming, erasing, and reading of cells 10, 50, and 60 which employ transistor 70 are provided below in Tables 10, 11, and 12, respectively.

Table 10

Electrical bias conditions					
Mode	Bit line	Select Gate	Source	N-well	Control Gate
Program (option 1)	0V	0V	5-15V	5-15V	ramp up to desired $V_p$
Program (option 2)	0V	0V	5-15V	5-15V	desired $V_p$
Erase (option 1)	3-15V	0V	3-15V	3-15V	-3 to -15V

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Table10 (continued)

Electrical bias conditions					
Mode	Bit line	Select Gate	Source	N-well	Control Gate
Erase (option 2)	15-22V	0V	15-22V	15-22V	0V
Read (option 1)	less than Vcc	0V	Vcc	Vcc	0V to Vcc
Erase (option 2)	pre-charge to Vcc	0V	0V	Vcc	0V

Table 11

	Bit line	Drain select gate	Source select gate	Source	N-well	Cell control gate
Program (option 1)	V <sub>p</sub>	0V	3-15V	3-15V	3-15V	-3 to -15V
Program (option 2)	V <sub>p</sub>	0V	15-22V	15-22V	15-22V	0V
Erase	0V	0V	*	5-15V	5-15V	5-17V
Read (option 1)	less than Vcc	0V	0V	Vcc	Vcc	0 to Vcc
Read (option 2)	pre-charge to Vcc	0V	0V	0V	Vcc	0V

\* 0 to (source voltage - 1V)

Table 12

Electrical bias conditions					
Mode	Bit Line	Select Gate	Source	N-well	Control Gate
Program (option 1)	0V	0V	5V-15V	5V-15V	desired V <sub>p</sub> , i.e. (5-17V)
Program (option 2)	0V	0V	5V-15V	5V-15V	ramp up to desired V <sub>p</sub>
Erase (option 1)	3V-15V	0V	3V-15V	3V-15V	-3V to -15V
Erase (option 2)	15V-22V	0V	15V-22V	15V-22V	0V
Read (option 1)	less than Vcc	0V	Vcc	Vcc	0 to Vcc
Read (option 2)	pre-charge to Vcc	0V	0V	Vcc	0V

[0031] The advantageous operational characteristics of the above described memory cells allow for such cells to be fabricated by a process simpler than those conventional processes used to fabricate N-channel single-poly non-volatile memory cells. The fabrication of cell 10 will be described below in the context of a large CMOS structure 100 which includes PMOS and NMOS peripheral transistors (these peripheral transistors may be used for instance as address decoders, current sensors, select transistors, and on). Although described below in the context of fabricating cell 10 in a twin well structure, it is to be noted that the process described below may be easily modified so that cell 10 may be formed in an N-well structure. Further, the process described below may also be used to fabricate cells 50, 60 and 70 using either single or twin well technology, and is equally applicable to those cells which employ as storage elements transistor 70.

[0032] Referring now to Figure 13, structure 100 includes a P-type substrate 102 having formed by conventional means therein an N-well 104 and a P-well 106. The resistivity and thickness of N-well 104 and P-well 106 will depend upon the desired characteristics of the devices to be formed therein. A LOCOS process is used to form isolation regions which will electrically insulated later-formed transistor from one another. Field oxide regions 108 approximately 7500 Å thick and a layer of sacrificial oxide (not shown) approximately 240 Å thick are formed on a top surface of substrate 102 by any suitable means.

[0033] Structure 100 is masked by any suitable means (not shown) such as for instance photoresist. P-type dopants such as BF<sub>2</sub> are implanted at an energy of 50 keV and a dosage of 1E14 ions/cm<sup>2</sup> into N-well 104 to form a P diffusion



region 36 which will serve as the control gate for cell 10 (see also Figure 2). The mask is then removed.

[0034] A layer of poly-silicon is deposited over a top surface of field oxide regions 108 and gate oxide 110 and selectively etched to form the pattern shown in Figure 13. Portions 114a and 116a will serve as gates for NMOS peripheral transistors 114 and 116, respectively, while portions 118a and 120a will serve as gates for PMOS peripheral transistors 118 and 120, respectively. Portion 122 may serve as an interconnection between devices formed within structure 100. Portion 26 will serve as the floating gate of cell 10.

[0035] The process steps used for threshold voltage implants and channel stop implants for cell 10 and peripheral transistors 114, 116, 118 and 120, as well as for the formation of tunnel oxide 34 and oxide layer 40 separating floating gate 26 from control gate 36 of cell 10, are not shown in the Figures or discussed herein for simplicity. Preferably, Arsenic is implanted at an energy of 100 keV and a dosage of approximately of  $2 \times 10^{13}$  ions/cm<sup>2</sup> or Phosphorus at an energy of 50 keV and a dosage of  $2 \times 10^{13}$  ions/cm<sup>2</sup> to serve as the threshold voltage implant for cell 10. Further, gate oxide layer 110 may also be implemented according to well known techniques and are thus described herein. Note, however, that as discussed above with respect to Figure 3A, it is not necessary to open a tunnel window in tunnel oxide layer 34, thereby saving at least one masking step over conventional processes used to form N-channel single-poly EEPROM cells. Note that these just described process steps should be performed before the formation of gates 114, 116, 118, and 120, floating gate 26 and contact 122.

[0036] Referring now to Figure 14, PMOS cell 10 and PMOS transistors 118, and 120 are masked (not shown). N-type dopants such as Phosphorus are implanted at an energy of approximately 40 keV and a dosage of approximately  $3 \times 10^{13}$  ions/cm<sup>2</sup> into P-well 106 to form N-type regions 114b, 115a, and 116b. The mask is then removed.

[0037] NMOS transistors 114 and 116 are then masked (not shown) and P-type dopants such as BF<sub>2</sub> are implanted at an energy of approximately 60 keV and a dosage of approximately  $7 \times 10^{12}$  ions/cm<sup>2</sup> into N-well 104 to form N-regions 118b, 118c, 120b, and 120c. Sidewall oxide spacers 124 are then formed by conventional means on the sides of control gates 114, 116, 118, and 120, layer 122, and floating gate 26.

[0038] PMOS cell 10 and PMOS peripheral transistors 118 and 120 are again masked and N-type dopants, preferably Arsenic, are implanted at an energy of 80 keV and a dosage of  $6 \times 10^{15}$  ions/cm<sup>2</sup> into P-well 106 to form N<sup>+</sup> diffusion regions 114c, 115b, and 116c, as shown in Figure 13. N-/N<sup>+</sup> diffusion region 114b/114c serves as the source for NMOS transistor 114, N-/N<sup>+</sup> diffusion region 115a/115b serves as the drain for NMOS transistor 114 and the source for NMOS transistor 116, and N-N<sup>+</sup> diffusion region 116b/116c serves as the drain for NMOS transistor 116. The PMOS mask is then removed.

[0039] Structure 100 is again masked and the sidewall spacers 124 (not shown) on the source and drain sides of floating gate 26 are dipped and removed. This ensures that in a subsequent doping step the source and drain regions (see Figure 3A) of cell 10 will be of a P<sup>+</sup> diffusion structure, as opposed to the lightly doped drain (LDD) structure of P-/P<sup>+</sup> diffusion region 118c/118e. After this mask is removed, NMOS peripheral transistors 114 and 116 are masked and P-type implants, preferably BF<sub>2</sub>, are implanted at an energy of 50 keV and a dosage of  $2 \times 10^{15}$  ions/cm<sup>2</sup> into N-well 104 to form P<sup>+</sup> regions 118d, 118e, 120d, and 120e, as well as P<sup>+</sup> source 20 and P<sup>+</sup> drain 22 regions (see Figure 3) of cell 10. The P-/P<sup>+</sup> diffusion regions 118b/118d and 118c/118e serve as the source and drain regions, respectively, of PMOS transistor 118, while P-/P<sup>+</sup> diffusion regions 120b/120d and 120c/120e serve as the source and drain regions, respectively, of PMOS transistor 120.

[0040] The remaining portions of structure 100 may be completed according to well known fabrication techniques.

[0041] The process described above with respect to Figures 13 and 14 requires fewer masking steps than do conventional processes used in the fabrication of N-channel single poly memory cells. Since the source and drain regions of cell 10 may be formed simultaneously with the source and drain regions of PMOS peripheral transistors 118 and 120, an additional masking step is saved. Further, since as described earlier the operation of cell 10 does not require high voltages across its drain/N-well junction, neither N-channel or P-channel high voltage implants are necessary, thereby resulting in a further elimination of masking steps. In this manner, the fabrication of cell 10 may be realized while reducing manufacturing costs.

[0042] It is to be noted that the above described fabrication process may be easily adapted to construct memory cells employing as memory elements single-poly transistors 70. Furthermore, the polarities of the bipolar and MOS transistors may be reversed while still realizing the benefits of the above described invention.

[0043] In yet another memory cell the structure of cell 10 is modified and an additional diffusion region added thereto so as to allow for lower erase voltages. Those components common to cell 200 and cell 10 are appropriately labelled with the same numerals.

[0044] Referring collectively to Figures 15-20, cell 200 includes a storage transistor 202, a select transistor 204, and an erase transistor 206 separated by field oxide regions OX. P<sup>+</sup> diffusion region 208 serves as the source for storage transistor 202, P<sup>+</sup> diffusion region 210 serves as both the drain for storage transistor 202 and the source for select transistor 204, and P<sup>+</sup> diffusion region 212 serves as the drain of select transistor 204 (see Figures 18). A bit line BL is coupled to drain 212 of select transistor 204 via a contact 213. P<sup>+</sup> diffusion regions 214 and 216 serve as the source and drain, respectively, of erase transistor 206 (see Figure 20). A contact 217 couples drain 216 of erase transistor

206 to an erase line EL. A poly-silicon layer 218 serves as the floating gate of storage transistor 202, and a polysilicon layer 220 serves as the gate for both select transistor 204 and erase transistor 206. Application of a bias voltage to gate 220 enhances a channel 222 extending between source 210 and drain 212 of select transistor 204 and enhances a channel 224 extending between source 214 and drain 216 of erase transistor 206.

**[0045]** A P-type buried diffusion layer 226 serves as the control gate of storage transistor 202 and has formed therein a P+ contact region 228 (see Figures 15 and 17). A layer of oxide 229 approximately between 80-350 Å thick is provided between control gate 226 and floating gate 218. An opening in insulating layer 230 and oxide 229 enables electrical contact with buried control gate 226 via a P+ contact region 228. A tunnel oxide layer 234 preferably between 80-130 Å thick is provided between floating gate 218 and a P-type diffusion region 215, which serves as an erase gate, to facilitate the tunneling of electrons from floating gate 218 to P-type diffusion region 215. In some embodiments, tunnel oxide layer 234 extends between floating gate 218 and a portion of P+ diffusion region 214 to also facilitate electron tunneling from floating gate 218 to a portion of P+ diffusion region 214. Floating gate 218 and control gate 226 form an MOS capacitor in the same manner as that of conventional N-channel EEPROM cells. Note, however, that unlike conventional N-channel single-poly memory cells, it is not necessary to open a tunnel window in tunnel oxide layer 234 of cell 200.

**[0046]** Cell 200 has in its unprogrammed state a threshold voltage  $V_t$  equal to approximately -4.5 V. To program cell 200, bit line BL and select gate 220 are grounded while source 208 of storage transistor 202, N-well 12, and erase line EL (which is coupled to drain 216 of erase transistor 206) are held at approximately 7 V. A program voltage which ramps from 0 to approximately 12 V is coupled to control gate 226 via P+ contact region 228. A fraction of the resultant voltage on control gate 226 is capacitively coupled to floating gate 218. In the preferred embodiment, the ramping of the voltage of control gate 226 from 0 to 12 V results in approximately 7.5 V being coupled to floating gate 218. Note that the precise amount of voltage so coupled to floating gate 218 depends upon the coupling ratio between control gate 226 and floating gate 218.

**[0047]** The application of the above-described voltages causes positively charged holes to accelerate across channel 232 from source 208 to drain 210. These holes collide with electrons in a depletion region proximate drain 210 and thereby generate high energy electrons which, being attracted to the positively charged floating gate 218, are injected from the depletion region into floating gate 218. The resultant negative charge on floating gate 218 depletes channel region 232 and forces cell 200 into deep depletion. When programmed as such, cell has a  $V_t$  equal to approximately 1 V. In some cells, a current limiting device (not shown) is coupled to bit line BL to prevent programming currents from exceeding approximately 100  $\mu$ A, thereby limiting power consumption during programming.

**[0048]** Cell 200 is erased by grounding select gate 220, bit line BL, and source 208 of storage transistor 202, while applying approximately 8 V to erase line EL and applying approximately -8 V to control gate 226. N-well 12 is maintained either at approximately ground potential or a floating potential during erasing. This electrical bias condition causes electrons to tunnel from floating gate 218 through tunnel oxide layer 234 into erase gate 215 and a portion of P+ diffusion region 214, thereby returning the threshold voltage of storage transistor 202 to its normal erased state value of approximately -4 V. Note that during erasing operations electrons do not tunnel from floating gate 218 into channel 232, source 208, or drain 210 of storage transistor 202.

**[0049]** Erasing floating gate 218 in the manner described above allows for lower erase voltages and also allows for cell 200 to handle higher read currents, and thereby operate at higher speeds, without undesirably increasing the size dimensions of cell 200, as will be described below. It is known that the amount of read current realizable by a memory cell may be increased by increasing the width of the channel region. In a single-poly memory cell the ratio between the voltage applied to the buried control gate and the voltage coupled to the floating gate (the coupling ratio) is equal to  $C_2/(C_1 + C_2)$ , where  $C_1$  is the capacitance of the channel region and  $C_2$  is the capacitance of the buried control gate. Thus, increasing the width of the channel region, and thus the capacitance of the channel region, undesirably reduces the coupling ratio which, in turn, requires higher voltages to be applied to the control gate in order for a sufficient program voltage to be coupled to the floating gate. Although a decrease in the coupling ratio may be offset by increasing the surface area and thus the capacitance of the control gate, even minimal increases in the above described coupling ratio would require significant increases in the surface area of the control gate, thereby undesirably increasing the size of the memory cell.

**[0050]** The above-described erasing operation of cell 200 eases this trade-off. The grounding of channel region 232 results in channel regions 232 having a minimal capacitance, while the positive bias applied to erase gate 215 results erase gate 215 having a capacitance  $C_3$ . With bias conditions, the coupling ratio of cell 200 during erasing operations is  $C_2/(C_2 + C_3)$ . Thus, by minimizing the width of erase gate 215, the coupling ratio may be maximized during erasing operations. Thus, the employment of erase gate 215 in cell 200 allows an increased read speed to be attained without undesirably increasing the size of cell 200 and/or requiring higher erase voltages.

**[0051]** Where it is desired to read cell 200, source 208 and N-well 12 are held at  $V_{cc}$  while select gate 220 is grounded. Control gate 226 is held at a voltage of approximately  $V_{cc} - 2V$ , and a read voltage of approximately  $V_{cc} - 2V$  is applied to bit line BL. Cell 200 will conduct channel current only if cell 200 is programmed, i.e., only if there is negative charge

stored in floating gate 218. Thus, since a read current flows through cell 200 when floating gate 218 is negatively charged, a programmed cell 200 does not suffer from read disturb problems characteristic of conventional N-channel EEPROM or flash cells. When cell 200 is in an erased state, the voltage on floating gate 218 is always less than the voltage on drain 210. In this manner, cell 200 does not exhibit read disturb problems when in an erased state.

[0052] Acceptable ranges for the above-described reading, erasing, and programming bias conditions for cell 200 are provided below in Table 13.

Table 13

Electrical bias conditions						
Mode	Bit Line	Select Gate	Source	N-well	Control Gate	Erase Line
Program	0V	0V	5-8V	5-8V	ramped from 0V to 12V	5-8V
Erase	0V	0V	0V	3-13V	-3 to -13V	3-13V
Read	less than Vcc	0V	Vcc	Vcc	0 to Vcc	float or 0V

[0053] It is to be noted that the advantages described above with respect to cell 10 realized by employing a P-channel memory cell structure which is programmed by hot electron injection and erased by electron tunneling are equally applicable to the cells illustrated in Figures 15-20.

[0054] In accordance with the present invention, a PMOS single-poly non-volatile memory cell includes in a portion of the active region thereof a diffusion region which serves as an erase gate for the memory cell. Referring now to Figures 21, 22A, and 23, a P-channel single-poly cell 210 is formed in an N-well 312 provided within a P-type substrate 314 and includes a P-channel storage transistor 316 and a P-channel select transistor 318. In the description that follows, like components are similarly labelled. In some embodiments, N-well 312 has a sheet resistance of approximately 700-1200  $\Omega/\square$  and P-type substrate 314 has a resistivity of approximately 5-100  $\Omega\cdot\text{cm}$ . P+ diffusion region 320 serves as the source for storage transistor 316, P+ diffusion region 322 serves as both the drain for storage transistor 316 and the source for select transistor 318, and P+ diffusion region 324 serves as the drain for select transistor 318. Poly-silicon gates, 326 and 328 serve as the floating gate and select gate respectively of cell 310. Field oxide regions 329 define the active regions of cell 310.

[0055] Storage transistor 316 includes a P-type diffusion region 330 formed within N-well 312, where in some embodiments P-type diffusion region 330 has a sheet resistance of approximately 100-500  $\Omega/\square$ . An N-type diffusion region 332 having in some embodiments a sheet resistance of approximately 100-300  $\Omega/\square$  is formed within P-type diffusion region 330 and serves as the control gate for storage transistor 316. An N+ contact region 334 formed within control gate 332 allows for the coupling of voltages to control gate 332. A layer of tunnel oxide (not shown for simplicity) approximately 70-100 Å thick is provided between N-well 312 and floating gate 326.

[0056] To program cell 310 i.e. to charge floating gate 326 of storage transistor 316, N-well 312 is held at approximately ground potential while approximately -6.5 V is applied to drain 322 of storage transistor 316. Approximately 10 V is provided to control gate 332 via contact 334, while source 320 is allowed to float. The coupling ratio between control gate 332 and floating gate 326 is approximately 50%. Thus, approximately 5 V appears on floating gate 326. The voltage differential between floating gate 326 and drain 322 includes Fowler-Nordheim tunneling of electrons from drain 322 to floating gate 326 and also results in band-to-band tunneling induced injection of electrons from a portion of the channel region proximate P+ drain 322 into floating gate 326, thereby charging floating gate 326 and increasing the threshold voltage of storage transistor 316.

[0057] Note that the P/N junction formed by P-type diffusion region 330 and N-well 312 is forward biased during programming such that diffusion region 330 is at approximately 0.5 V. In this manner, P-type diffusion region 330 provides electrical isolation between N-well 312 and control gate 332 during programming operations, thereby allowing N-well 312 to be at ground potential while control gate 332 is at approximately 10 V. Further, since N-well 312 may be held at approximately ground potential during programming, the junction between N-well 312 and P+ drain 322 need only sustain approximately a 6.5 volt differential. This is in marked contrast to conventional single-poly memory cells whose well to drain junctions are typically required to sustain 15 volts or more. Minimizing the junction voltage between N-well 312 and P+ drain 322 allows the fabrication of cell 310 to be incorporated into single-poly processes typically used in the fabrication of logic circuitry associated with memory arrays without risk of incurring undesirable junction breakdown conditions.

[0058] Cell 310 also includes an N-type diffusion region 336 formed within a P-type diffusion region 340, where N-type diffusion region 336 serves as an erase gate for cell 310. In some embodiments, erase gate 336 has a sheet resistance of approximately 100-300  $\Omega/\square$  and P-type diffusion region 340 has a sheet resistance of approximately 100-500  $\Omega/\square$ . P-type diffusion region 340 electrically isolates erase gate 336 from N-well 312, as discussed below.

Note that in other embodiments the conductivity types of erase gate 336 and control gate 332 may be opposite that described above without departing from the scope of the present invention. A layer of tunnel oxide (not shown) approximately 70-100 Å thick is provided between floating gate 326 and erase gate 336.

[0059] To erase storage transistor 316, approximately -6.5 V is coupled to control gate 332 via contact 334. The P/N junction formed by P-type diffusion region 330 and control gate 332 becomes forward biased, where approximately -5.9 V appears on P-type diffusion region 330. Approximately -4.0 V is coupled from P-type diffusion region 330 and control gate 332 to floating gate 326. Source 320 is held at a floating potential and N-well 312 is grounded. Approximately 8 V is applied to erase gate 336. These voltage conditions facilitate the tunneling of electrons from floating gate 326 to erase gate 336. During erasing, approximately 0.5 V is coupled to P-type diffusion region 340, thereby reverse biasing the P/N junction formed by P-type diffusion region 340 and erase gate 336. In this manner, P-type diffusion region 340 isolates erase gate 336 from N-well 312 and prevents a current from flowing across from erase gate 336 to N-well 312.

[0060] The electrical isolation provided by P-type diffusion region 340 thus allows N-well 312 to remain at ground potential during erasing without an undesirable current flow from erase gate 336 to N-well 312. Thus, by minimizing the voltage differential between N-well 312 and P+ drain 322 during erasing, cell 310 may be fabricated using the same process flow used in constructing associated logic circuitry for cell 310. Accordingly, cell 310 and its associated logic circuitry may be easily fabricated on the same chip, thereby saving time, expense, and space.

[0061] As mentioned above, cell 310 utilizes Fowler-Nordheim tunneling for erasing operations and utilizes a combination of Fowler-Nordheim tunneling and hot electron injection for programming operations. As a result, cell 310 requires relatively low programming and erase voltages (10 and 8 V, respectively) and, thus, consumes little power during programming and erasing operations.

[0062] Cell 310 may be read by applying approximately 0.7 V to P+ drain 324 of select transistor 318 (i.e., the bit line) and approximately 3 V to control gate 332, P+source 320, and N-well 312. Erase gate 336 may either be floating or held at approximately 3 V. Note that cell 310 conducts a read current only if programmed, i.e., only if there is negative charge stored in floating gate 326. Thus, since a read current flows through cell 310 only when floating gate 326 is negatively charged, a programmed cell 10 does not suffer from read disturb problems characteristic of conventional N-channel memory cells such as flash and EEPROM. When cell 310 is in an erased state, the voltage on floating gate 326 is always less than the voltage on drain 322. In this manner, cell 310 does not exhibit read disturb problems when in an erased state. Table 14 below summarizes the voltage conditions for programming, erasing, and reading cell 310.

Table 14

operation	source 320	drain 322	control gate 332	erase gate 336	N-well 312
program	float	-6.5 V	10 V	0 V	0 V
erase	float	float	-6.5 V	8 V	0 V
read	3 V	2 V	3 V	float	3 V

[0063] In high endurance applications the structure of cell 310 may be problematic. Applicant suspects that during the fabrication of cell 310, nitride etching steps may create what is termed in the semiconductor industry as "white ribbons" in regions of the tunnel oxide proximate to field oxide regions. These white ribbons may begin to degrade the performance of cell 310 after repeated programming and erasing operations. Thus, in some embodiments in accordance with the present invention where cell 310 may be programmed and erased numerous times, an erase window is formed between erase gate 336 and floating gate 326.

[0064] Referring to Figure 24, a layer of oxide 338 approximately 200 Å thick is provided between floating gate 326 and erase gate 336. A window portion 338a approximately 70-100 Å thick is then formed within oxide layer 338, as shown in Figure 24, to facilitate electron tunneling from floating gate 326 and erase gate 336. The thicker oxide layer 338 prevents the formation of white ribbons during fabrication of cell 310 and, therefore, increases durability and reliability of cell 310.

[0065] In other embodiments, the erase gate structure may be slightly modified. In one such embodiment shown in Figure 22B, P-type diffusion region 340 may be eliminated, in which case erase gate 336 is formed directly within N-well 312. Although saving valuable silicon real estate, the absence of the electrically isolating diffusion region 340 results in the potential of erase gate 336 being the same as the potential of N-well 312. Accordingly, bit mode and byte mode erasing are not possible in the embodiment of Figure 22B since the erase gates 336 of each cell 310 formed within N-well 312 will necessarily be at the same potential, i.e., the potential of N-well 312.

[0066] Figures 22C and 22D show two further cells. In Figure 22C, which is an embodiment of the invention, erase gate 336a is a P-type diffusion region, as opposed to an N-type diffusion region. Note that in this embodiment the P/N junction formed by erase gate 336a and N-well 312 may be easily forward biased which, in turn, would undesirably

result in a current flow from erase gate 336a to N-well 312. In Figure 22D, which is present for reference purposes, the erase gate structure 336 is altogether eliminated.

[0067] In other cells (described for reference purposes) where size is of more significance than read speed, the channel width of storage transistor 316 may be reduced from its normal width of approximately 1-5  $\mu\text{m}$  to as little as approximately 0.3-0.7  $\mu\text{m}$ , and erase gate 336 may be eliminated. In such cells, cell 310 is programmed, erased, and read as described above except that the electrons will tunnel from floating gate 325 to P+ drain 322, source 320, and N-well 312. The reduction in channel width coupled with the elimination of erase gate 336 allows for up to a 30% reduction in cell size. Of course, this reduction in cell size comes at the expense of slower read speeds. Applicant has determined that such a reduction in cell size is warranted and will have a minimal effect upon performance speeds where read currents are less than approximately 50  $\mu\text{A}$ . Acceptable voltage conditions for programming, erasing, and reading such a reduced-size cell are provided below in Table 15.

Table 15

operation	source 320	drain 322	control gate 332	N-well 312
program	float	-6.5 V	10 V	0 V
erase	8 V	8 V	-6.5 V	8 V
read	3 V	2 V	3 V	3 V

[0068] Note that in still other embodiments, cell 310 may be programmed by coupling a sufficiently positive voltage such as, for instance, 0 V to floating gate 326 via control gate 332 while applying a negative bias voltage such as, for instance, -8 V to erase gate 336 to facilitate the tunneling of electrons from erase gate 336 to floating gate 326. In a similar manner, in some embodiments cell 310 may be erased by causing the tunneling of electrons from floating gate 326 to portions of N-well 312 proximate P+ source 320 and P+ drain 322 of storage transistor 316.

[0069] Cell 310 may also be incorporated into a memory array 350, as shown in Figure 25. It is to be understood that array 350 is shown in Figure 25 as including only two words (i.e. rows) of two bits (i.e. columns) for simplicity only. In actual embodiments, array 350 will normally include many words of many bits. Each of cells 310a-310d is formed in a common N-well such as N-well 312 and each has its P+ source 320 tied to a common source node CS. P+ drain 324 of each select transistor 318 is coupled to an associated one of bit lines BL. Note that cells 310a-310d are depicted in Figure 25 using a two-gate notation to illustrate the presence of control gate 326 and erase gate 336. The select gates 328, i.e. the gates of select transistors 318, in a common row are coupled to the gate of an erase select transistor 352 which has a source coupled to an erase gate potential EG and a drain coupled to erase gates 336 of each of cells 10 in a common row. The control gates 326 of each of cells 310 in a common row are coupled to the drain of a control gate select transistor 354 which has a gate coupled to a control gate bit line potential  $\text{CG}_B$  and a source coupled to a control gate word line potential  $\text{CG}_W$ .

[0070] To program, for instance, cell 310a, bit line  $\text{BL}_1$  is held at approximately -6.5 V, all other bit lines (e.g.  $\text{BL}_2$ ) are left floating, and erase gate select potential EG is held at 0 V. Select gate potential  $\text{SG}_1$  is held at approximately -8.5 V and, in turning on associated select transistors 318 and associated erase transistor 352, pulls drain 322 and erase gate 336 of selected cell 310a to approximately -6.5 V and 0 V, respectively. Drains 322 of unselected cells 310 (e.g. cell 310b) are floating. Control gate bit line  $\text{CG}_B$  is pulled to ground potential to turn on control gate select transistors 354. Control gate word line  $\text{CG}_W$  associated with cell 310a is pulled to approximately 10 V, thereby coupling approximately 5 V to floating gate 326 of selected cell 310a, as described above. In this manner, cells 310 of array 350 may be programmed in a bit-by-bit fashion. A summary of voltage conditions for programming, erasing, and reading cells 310 of array 350 is provided below in Table 16, where F denotes a floating potential.

Table 16

mode	cell	location	SG	BL	$\text{CG}_\Omega$	$\text{CG}_\Phi$	EG	source	N-well
program	selected		-8.5	-6.5	0.5	8	F	F	0
program	unselected	same row	0.5	-6.5	0.5	F	F	F	0
program	unselected	same column	-8.5	F	8	8	F	F	0
erase	unselected		10	F	-8.5	-6.5	8	F	F
erase	unselected	same row		F	-8.5	F	8	F	F
erase	unselected	same column		F	0.5	-6.5	F	F	F

Table 16 (continued)

mode	cell	location	SG	BL	CG $\Omega$	CG $\diamond$	EG	source	N-well
read	unselected			0.7	0.5	3	F	3	3
read	unselected	same row		0.7	0.5	3	F	3	3
read	unselected	same column		F	0.5	3	F	3	3

## Claims

1. A P-channel non-volatile memory cell having a P+ source (320) and a P+ drain (322) formed in an N-well (312), a channel extending between said source and said drain, a floating gate (326) overlying said channel, and a first diffusion region (332) formed in said N-well and underlying a first portion of said floating gate, said first diffusion region serving as a control gate of said cell; said memory cell being characterized by
  - a second diffusion region (336) formed in said N-well and underlying a second portion of said floating gate, said second diffusion region serving as an erase gate of said cell; and
  - a third diffusion region (330) formed in said N-well, wherein said control gate (332) is formed within said third diffusion region, and wherein said third diffusion region is of a conductivity type opposite that of said control gate and of said well to electronically isolate said control gate from said N-well.
2. The memory cell of Claim 1, further comprising a fourth diffusion region (340) formed in said N-well, said fourth diffusion region being of a conductivity type opposite that of said erase gate, wherein said erase gate (336) is formed within said fourth diffusion region (340) whereby said fourth diffusion region electrically isolates said erase gate from said N-well.
3. The memory cell of Claim 2, wherein said fourth diffusion region (340) is P-type.
4. The memory cell of Claim 3, wherein said third diffusion region is (330) P-type.
5. The memory cell of Claim 1, wherein said second diffusion region is (336a) N-type.
6. The memory cell of Claim 1, or 2, wherein said control gate is N-type.
7. The memory cell of Claim 1, or 2, wherein said erase gate is P-type.
8. The memory cell of Claim 1, or 2, wherein said erase gate is N-type.
9. A method of operating a P-channel non-volatile memory cell, said cell comprising a P+ source (320) and a P+ drain (322) formed in an N-well (312), a channel extending between said source and said drain, a floating gate (326) overlying said channel, a first diffusion region (332) formed in said N-well and underlying a first portion of said floating gate, said first diffusion region serving as a control gate of said cell, and a second diffusion region (336) formed in said N-well and underlying a second portion of said floating gate, said second diffusion region serving as an erase gate of said cell, and a third diffusion region (330) formed in said N-well, wherein said control gate (332) is formed within said third diffusion region and wherein said third diffusion region is of a conductivity type opposite to that of said control gate and of said well, said method being characterized by tunneling electrons from said drain (322) to said floating gate (326) and injecting hot electrons from a portion of said channel proximate said drain to said floating gate to program said memory cell, said control gate (332) being electrically isolated from said N-well (312).
10. The method of Claim 9, wherein said memory cell is programmed by applying approximately -6.5 volts to said drain, applying approximately 10 volts to said control gate, coupling said source to a floating potential, and grounding said N-well.
11. The method of Claim 9 or 10, further comprising tunneling electrons from said floating gate to said erase gate to erase said memory cell.

12. The method of Claim 9, 10 or 11, wherein said memory cell is erased by applying approximately -6.5 volts to said control gate, applying approximately 8 volts to said erase gate, and coupling said source, said drain, and said N-well to a floating potential.

## Patentansprüche

1. Nichtflüchtige P-Channel-Speicherzelle umfassend eine P+ Source (320) und einen P+ Drain (322), die in einem n-leitenden Quellbereich (312) ausgebildet sind, einen sich zwischen der Source und dem Drain erstreckenden Channel, ein potentialfreies Gate (326) über dem Channel und einen ersten Diffusionsbereich (332), der in dem n-leitenden Quellbereich ausgebildet ist und unter einem ersten Teil des potentialfreien Gates liegt, wobei der erste Diffusionsbereich als Kontrollgate der Zelle dient, gekennzeichnet durch
  - einen zweiten Diffusionsbereich (336), der in dem n-leitenden Quellbereich ausgebildet ist und unter einem zweiten Teil des potentialfreien Gates liegt, wobei der zweite Diffusionsbereich als Löschgate der Zelle dient, und
  - einen dritten Diffusionsbereich (330), der in dem n-leitenden Quellbereich ausgebildet ist, wobei das Kontrollgate (332) im dritten Diffusionsbereich ausgebildet ist und der dritte Diffusionsbereich von einem zu dem Kontrollgate und dem Quellbereich entgegengesetzten Leitungstyp ist, um das Kontrollgate elektronisch von dem n-leitenden Quellbereich zu isolieren.
2. Speicherzelle nach Anspruch 1, ferner umfassend einen vierten Diffusionsbereich (340), der in dem n-leitenden Quellbereich ausgebildet ist, wobei der vierte Diffusionsbereich von einem zu dem Löschgate (336) entgegengesetzten Leitungstyp ist, das Löschgate im vierten Diffusionsbereich (340) ausgebildet ist und der vierte Diffusionsbereich das Löschgate elektrisch von dem n-leitenden Quellbereich isoliert.
3. Speicherzelle nach Anspruch 2, wobei der vierte Diffusionsbereich (340) p-leitend ist.
4. Speicherzelle nach Anspruch 3, wobei der dritte Diffusionsbereich (330) p-leitend ist.
5. Speicherzelle nach Anspruch 1, wobei der zweite Diffusionsbereich (336a) n-leitend ist.
6. Speicherzelle nach Anspruch 1 oder 2, wobei das Kontrollgate n-leitend ist.
7. Speicherzelle nach Anspruch 1 oder 2, wobei das Löschgate p-leitend ist.
8. Speicherzelle nach Anspruch 1 oder 2, wobei das Löschgate n-leitend ist.
9. Verfahren zum Betreiben einer nichtflüchtigen P-Channel-Speicherzelle, wobei die Zelle eine P+ Source (320) und einen P+ Drain (322), die in einem n-leitenden Quellbereich (312) ausgebildet sind, einen sich zwischen der Source und dem Drain erstreckenden Channel, ein potentialfreies Gate (326) über dem Channel, einen ersten Diffusionsbereich (332), der in dem n-leitenden Quellbereich ausgebildet ist und unter einem ersten Teil des potentialfreien Gates liegt, wobei der erste Diffusionsbereich als Kontrollgate der Zelle dient, einen zweiten Diffusionsbereich (336), der in dem n-leitenden Quellbereich ausgebildet ist und unter einem zweiten Teil des potentialfreien Gates liegt, wobei der zweite Diffusionsbereich als Löschgate der Zelle dient, und einen dritten Diffusionsbereich (330), der in dem n-leitenden Quellbereich ausgebildet ist, wobei das Kontrollgate (332) im dritten Diffusionsbereich ausgebildet ist und der dritte Diffusionsbereich von einem zu dem Kontrollgate und dem Quellbereich entgegengesetzten Leitungstyp ist, umfaßt, dadurch gekennzeichnet, daß
  - die Speicherzelle durch das Tunneln von Elektronen von dem Drain (322) zu dem potentialfreien Gate (326) und durch die Injektion heißer Elektronen von einem Teil des Channels in der Nähe des Drain in das potentialfreie Gate programmiert wird, wobei das Kontrollgate (332) elektrisch von dem n-leitenden Quellbereich (312) isoliert ist.
10. Verfahren nach Anspruch 9, wobei die Speicherzelle durch Anlegen einer Spannung von ungefähr -6,5 Volt an den Drain, Anlegen von ungefähr 10 Volt an das Kontrollgate, Anschließen der Source an ein potentialfreies Potential und Erden des n-leitenden Quellbereichs programmiert wird.

11. Verfahren nach Anspruch 9 oder 10, wobei die Speicherzelle durch Tunneln von Elektronen von dem potentialfreien Gate zu dem Löschgate gelöscht wird.
12. Verfahren nach Anspruch 9, 10 oder 11, wobei die Speicherzelle durch Anlegen von ungefähr -6,5 Volt an das Kontrollgate, Anlegen von ungefähr 8 Volt an das Löschgate und Anschließen der Source, des Drain und des n-leitenden Quellbereichs an ein potentialfreies Potential gelöscht wird.

## Revendications

1. Cellule de mémoire non volatile à canal P comportant une source P<sup>+</sup> (320) et un drain P<sup>+</sup> (322) formés dans un puits N (312), un canal qui s'étend entre ladite source et ledit drain, une grille flottante (326) qui s'étend au-dessus dudit canal et une première région de diffusion (332) formée dans ledit puits N et qui s'étend au-dessous d'une première partie de ladite grille flottante, ladite première région de diffusion jouant le rôle de grille de commande de ladite cellule, ladite cellule de mémoire étant caractérisée par :
  - une seconde région de diffusion (336) formée dans ledit puits N et qui s'étend au-dessous d'une seconde partie de ladite grille flottante, ladite seconde région de diffusion jouant le rôle de grille d'effacement de ladite cellule ; et
  - une troisième région de diffusion (330) formée dans ledit puits N, dans laquelle ladite grille de commande (332) est formée dans ladite troisième région de diffusion et dans laquelle ladite troisième région de diffusion est d'un type de conductivité opposé à celui de ladite grille de commande et dudit puits afin d'isoler électriquement ladite grille de commande vis-à-vis dudit puits N.
2. Cellule de mémoire selon la revendication 1, comprenant en outre une quatrième région de diffusion (340) formée dans ledit puits N, ladite quatrième région de diffusion étant d'un type de conductivité opposé à celui de ladite grille d'effacement, dans laquelle ladite grille d'effacement (336) est formée dans ladite quatrième région de diffusion (340) et ainsi, ladite quatrième région de diffusion isole électriquement ladite grille d'effacement vis-à-vis dudit puits N.
3. Cellule de mémoire selon la revendication 2, dans laquelle ladite quatrième région de diffusion (340) est de type P.
4. Cellule de mémoire selon la revendication 3, dans laquelle ladite troisième région de diffusion (330) est de type P.
5. Cellule de mémoire selon la revendication 1, dans laquelle ladite seconde région de diffusion (336a) est de type N.
6. Cellule de mémoire selon la revendication 1 ou 2, dans laquelle ladite grille de commande est de type N.
7. Cellule de mémoire selon la revendication 1 ou 2, dans laquelle ladite grille d'effacement est de type P.
8. Cellule de mémoire selon la revendication 1 ou 2, dans laquelle ladite grille d'effacement est de type N.
9. Procédé de fonctionnement d'une cellule de mémoire non volatile à canal P, ladite cellule comprenant une source P<sup>+</sup> (320) et un drain P<sup>+</sup> (322) formés dans un puits N (312), un canal qui s'étend entre ladite source et ledit drain, une grille flottante (326) qui s'étend au-dessus dudit canal, une première région de diffusion (332) formée dans ledit puits N et qui s'étend au-dessous d'une première partie de ladite grille flottante, ladite première région de diffusion jouant le rôle de grille de commande de ladite cellule, et une seconde région de diffusion (336) formée dans ledit puits N et qui s'étend au-dessous d'une seconde partie de ladite grille flottante, ladite seconde région de diffusion jouant le rôle de grille d'effacement de ladite cellule, et une troisième région de diffusion (330) formée dans ledit puits N, dans lequel ladite grille de commande (332) est formée dans ladite troisième région de diffusion et dans lequel ladite troisième région de diffusion est d'un type de conductivité opposé à celui de ladite grille de commande et dudit puits, ledit procédé étant caractérisé par :
  - un effet tunnel d'électrons depuis ledit drain (322) jusqu'à ladite grille flottante (326) et une injection d'électrons chauds depuis une partie dudit canal à proximité dudit drain jusqu'à ladite grille flottante afin de programmer ladite cellule de mémoire, ladite grille de commande (332) étant isolée électriquement vis-à-vis dudit puits N (312).
10. Procédé selon la revendication 9, dans lequel ladite cellule de mémoire est programmée en appliquant approximativement -6,5 volts audit drain, en appliquant approximativement 10 volts à ladite grille de commande, en cou-



plant ladite source à un potentiel flottant et en reliant à la masse ledit puits N.

11. Procédé selon la revendication 9 ou 10, comprenant en outre un effet tunnel d'électrons depuis ladite grille flottante jusqu'à ladite grille d'effacement afin d'effacer ladite cellule de mémoire.

12. Procédé selon la revendication 9, 10 ou 11, dans lequel ladite cellule de mémoire est effacée en appliquant approximativement -6,5 volts à ladite grille de commande, en appliquant approximativement 8 volts à ladite grille d'effacement et en couplant ladite source, ledit drain et ledit puits N à un potentiel flottant.

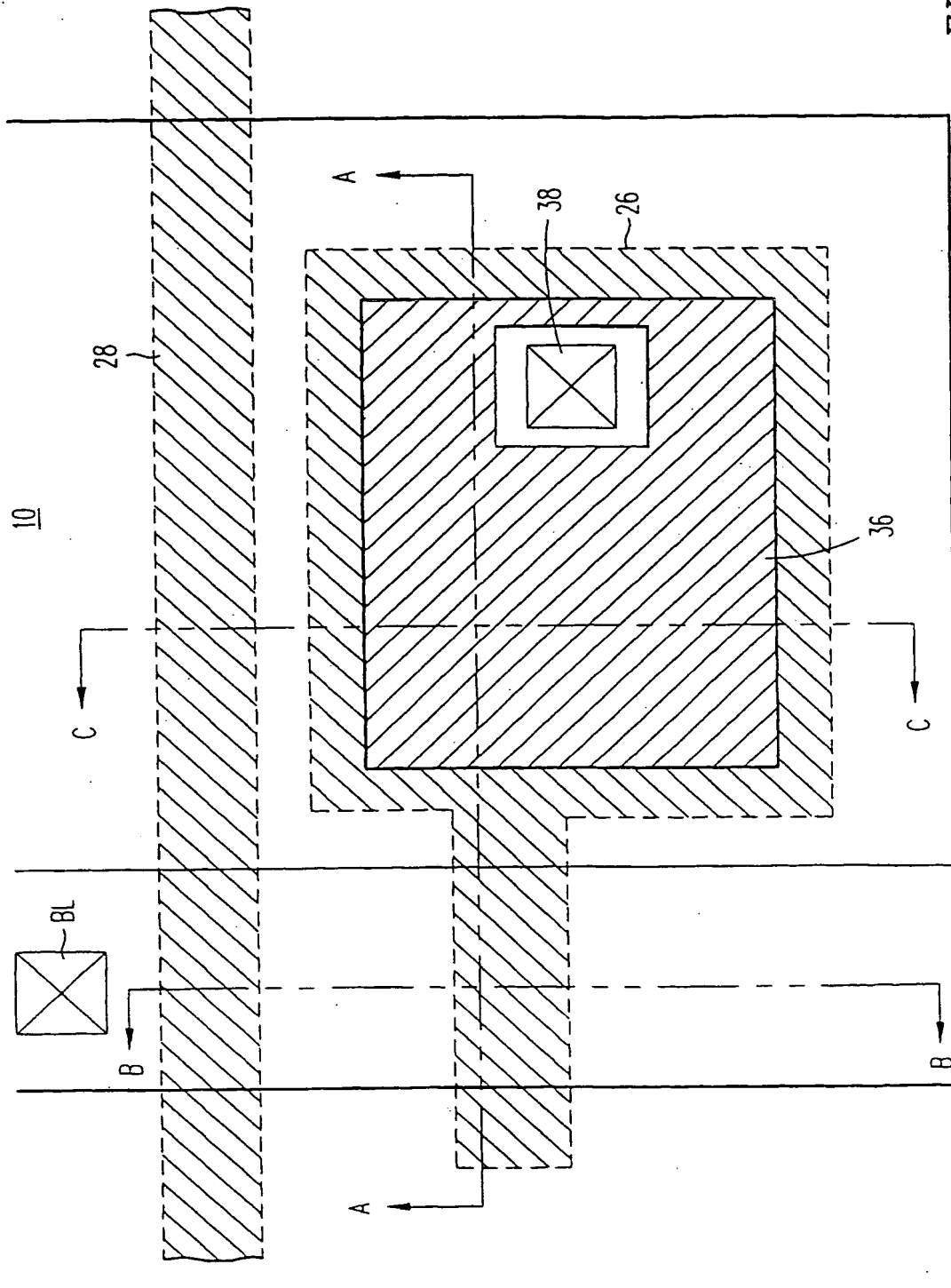


FIG. 1

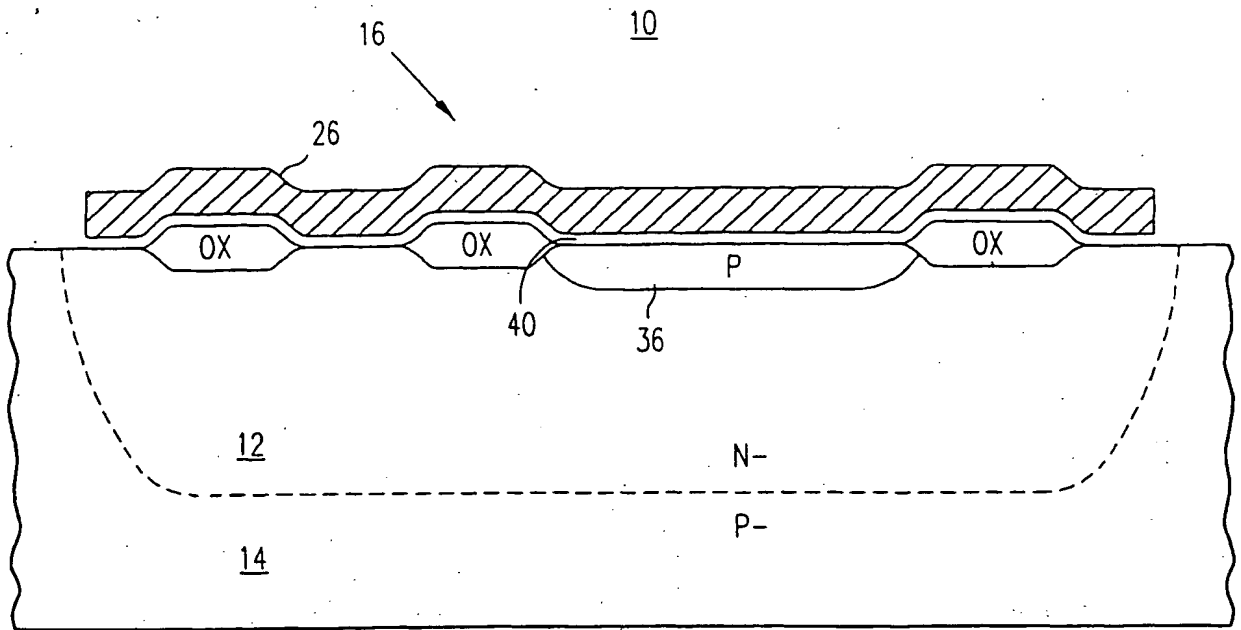


FIG. 2

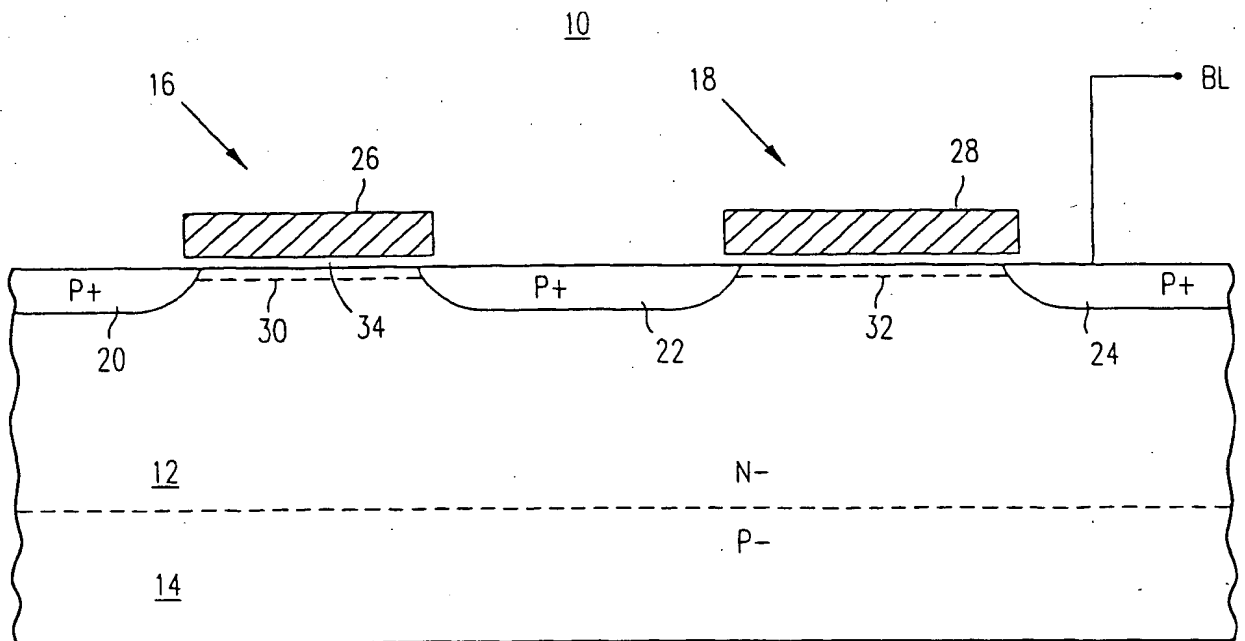


FIG. 3A

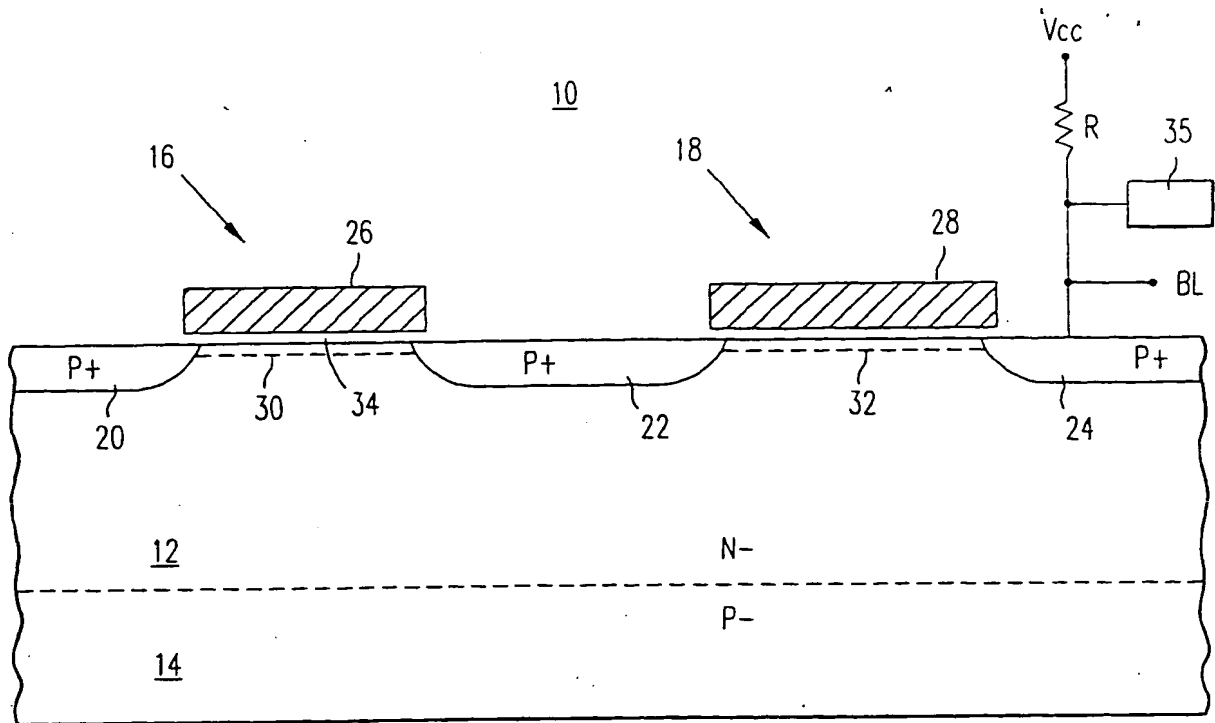


FIG. 3B

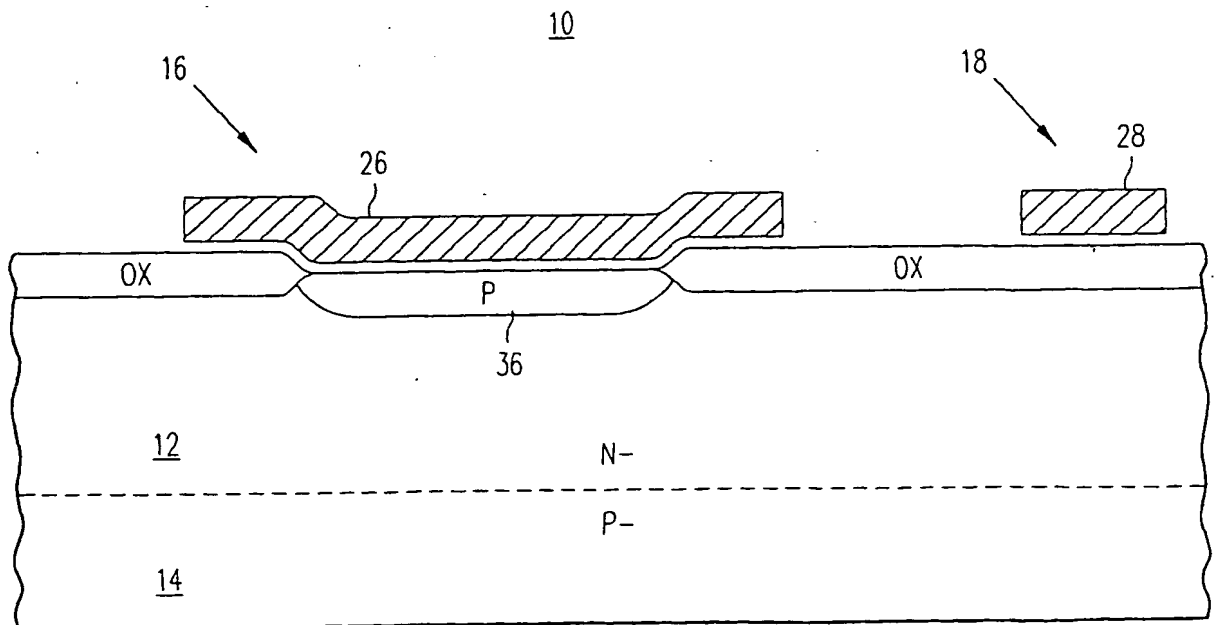


FIG. 4

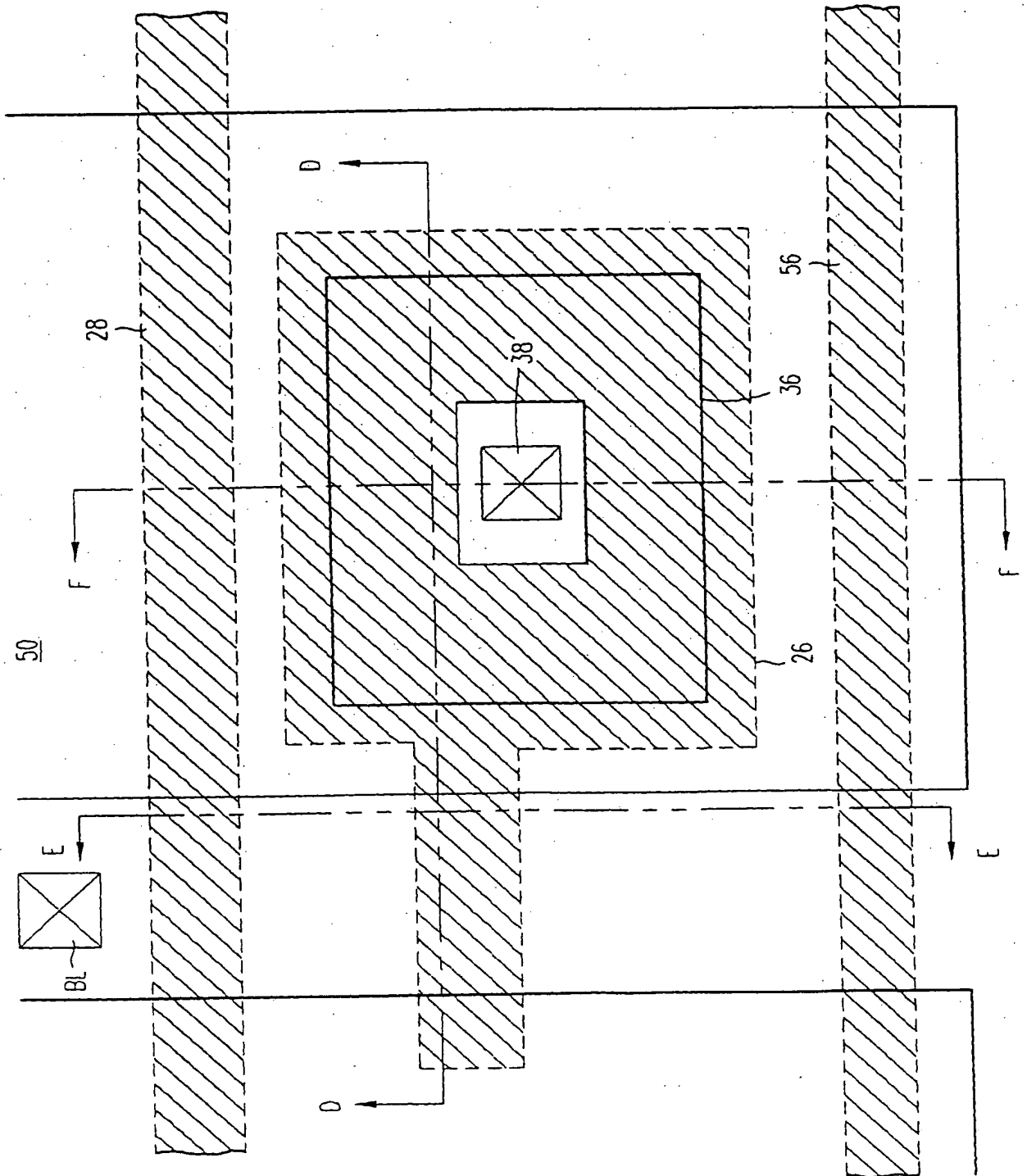


FIG. 5

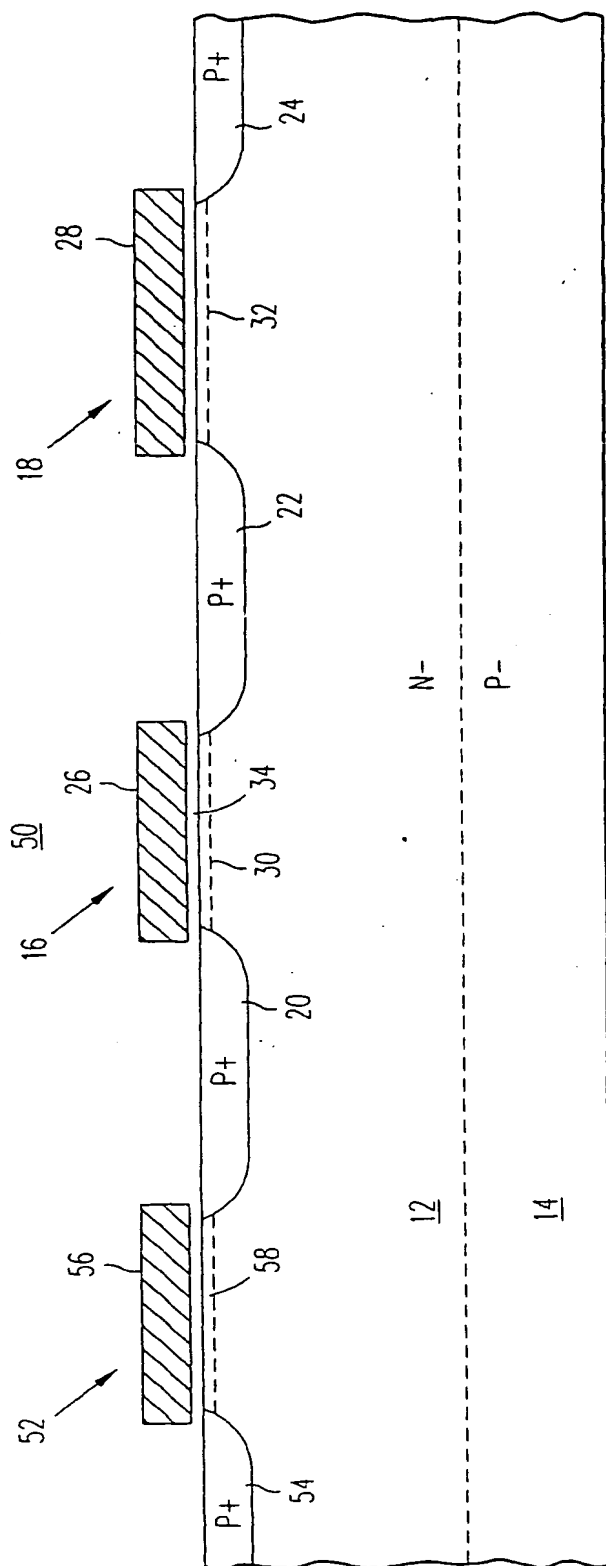


FIG. 6

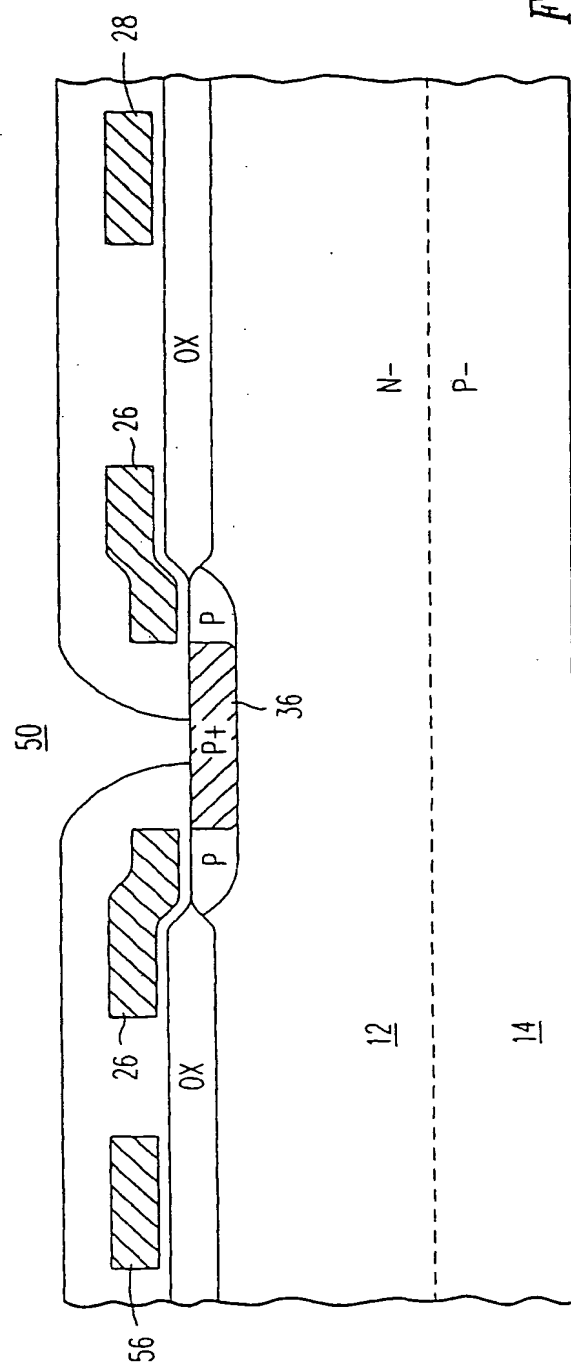


FIG. 7

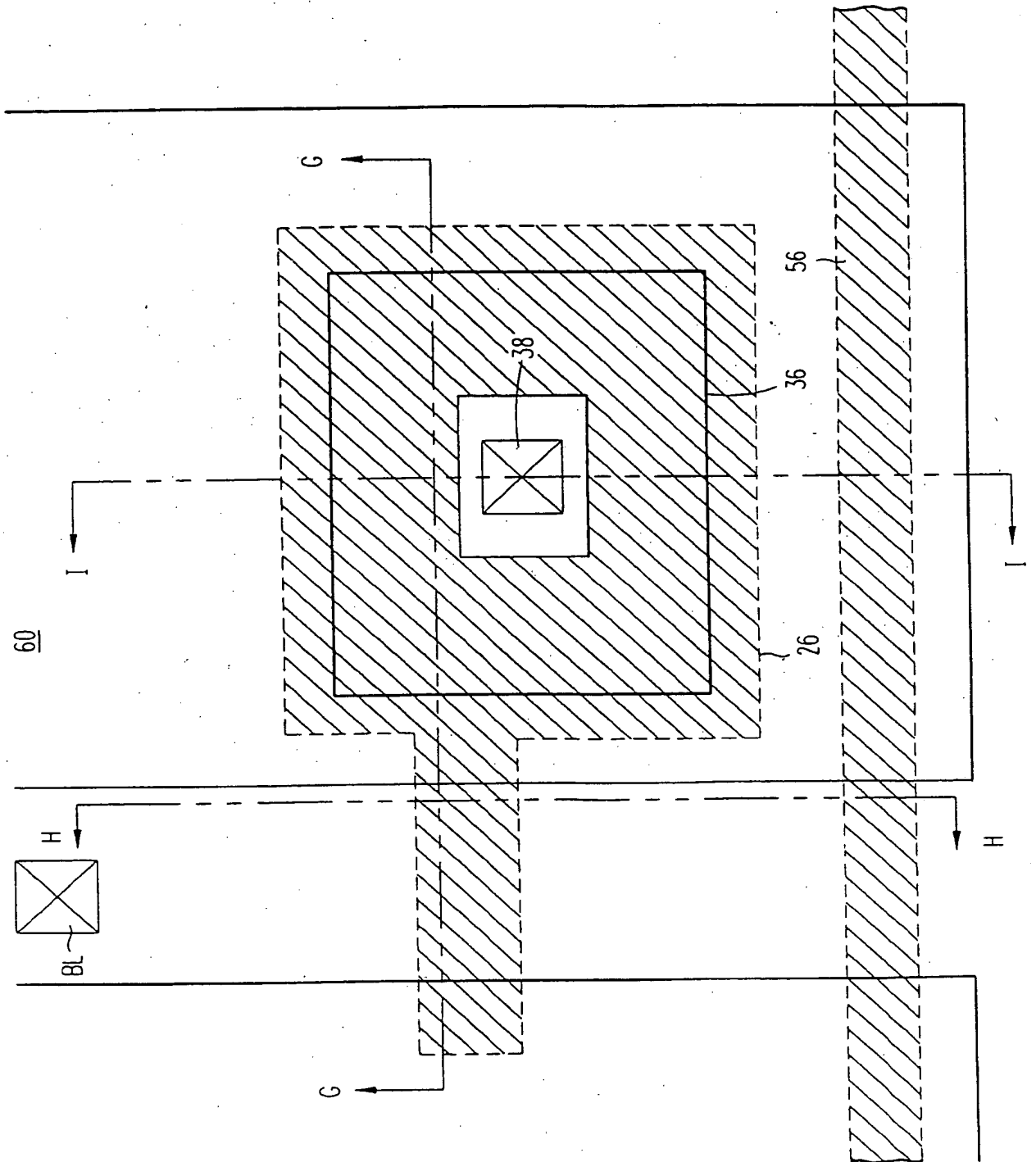


FIG. 8

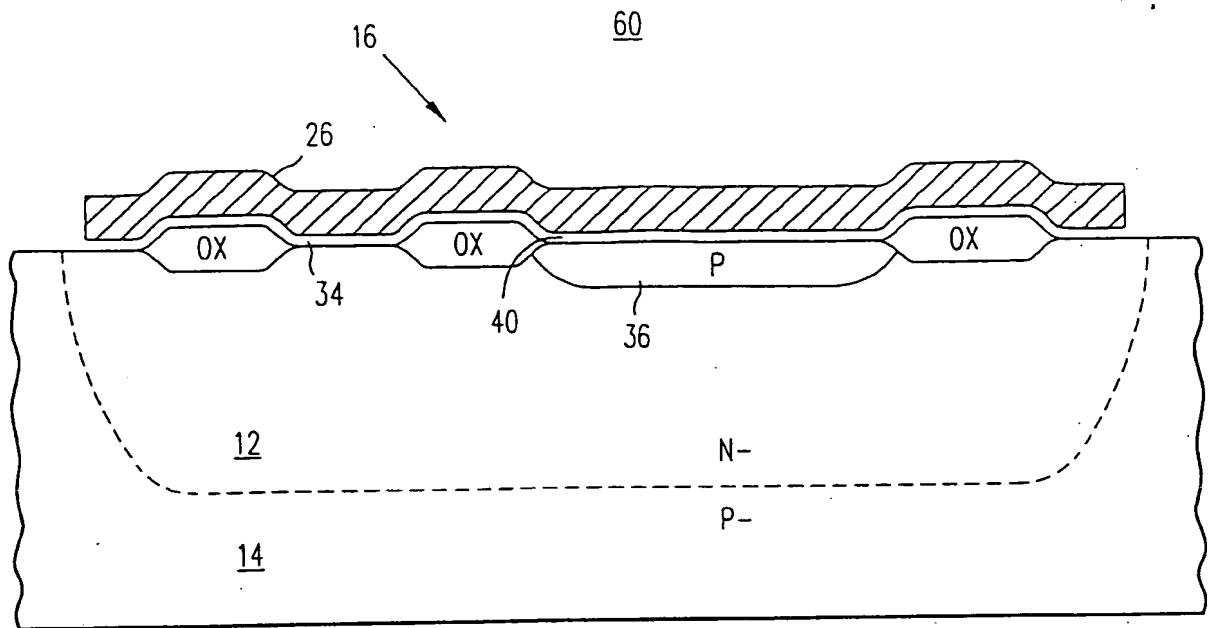


FIG. 9

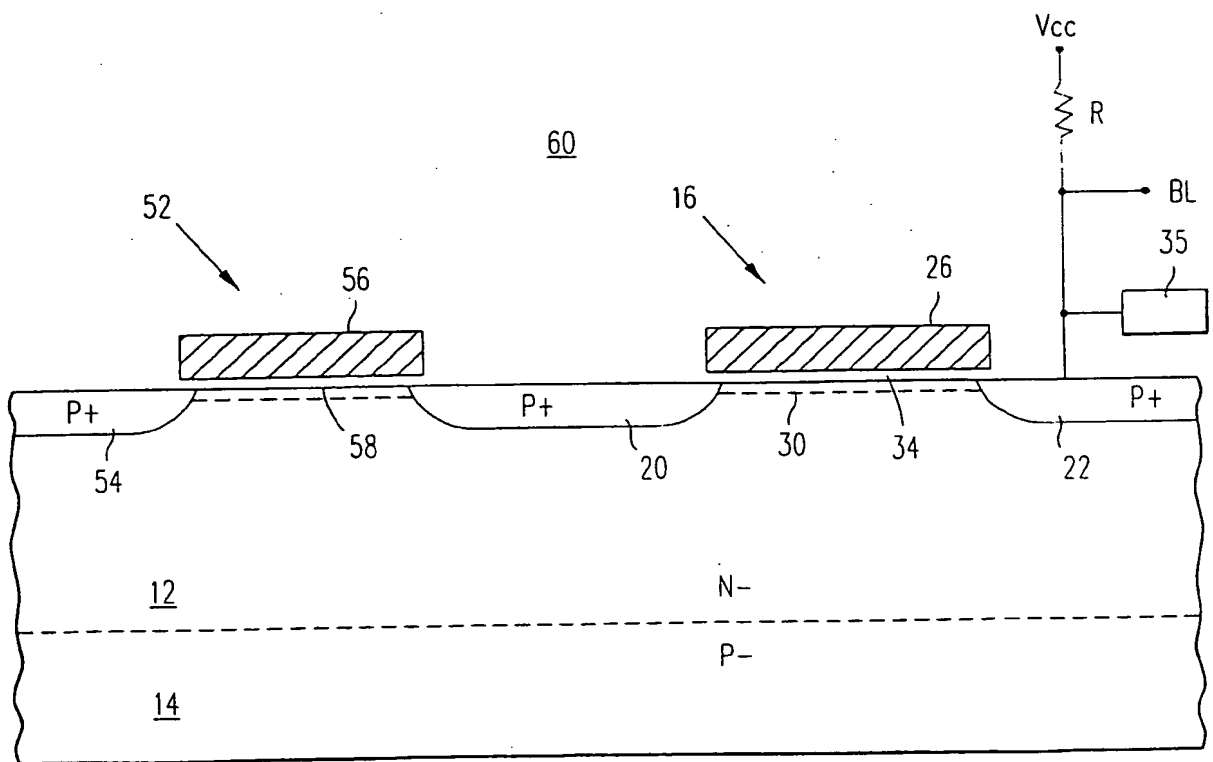


FIG. 10



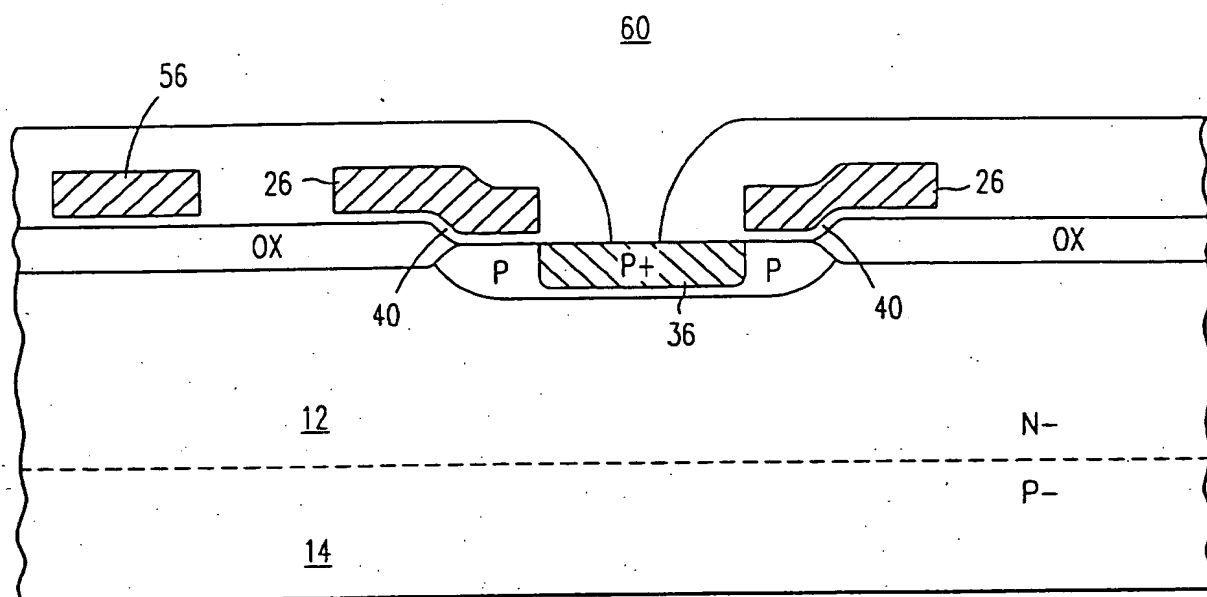


FIG. 11

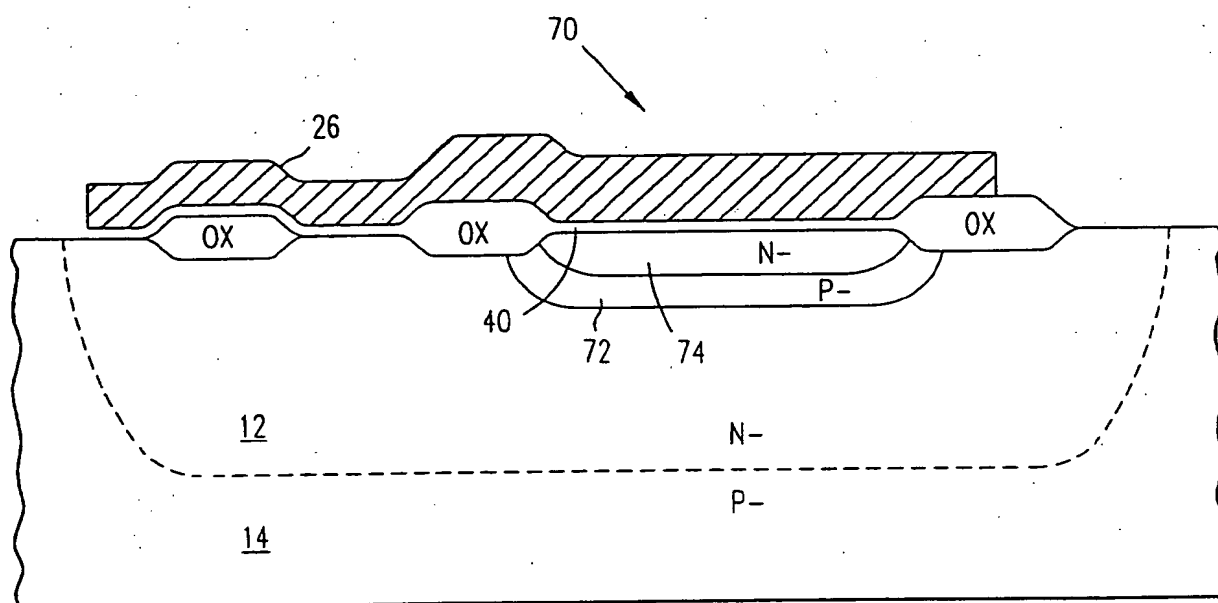


FIG. 12

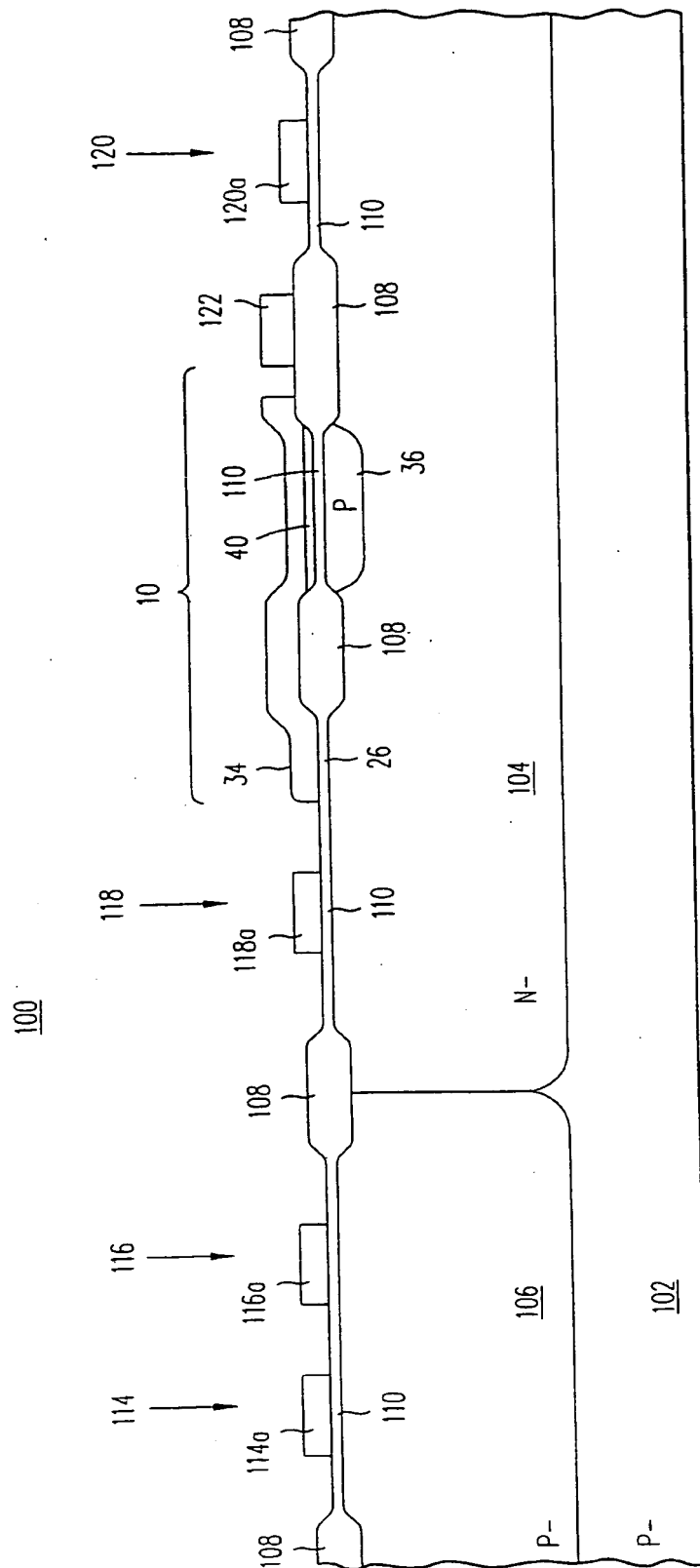


FIG. 13

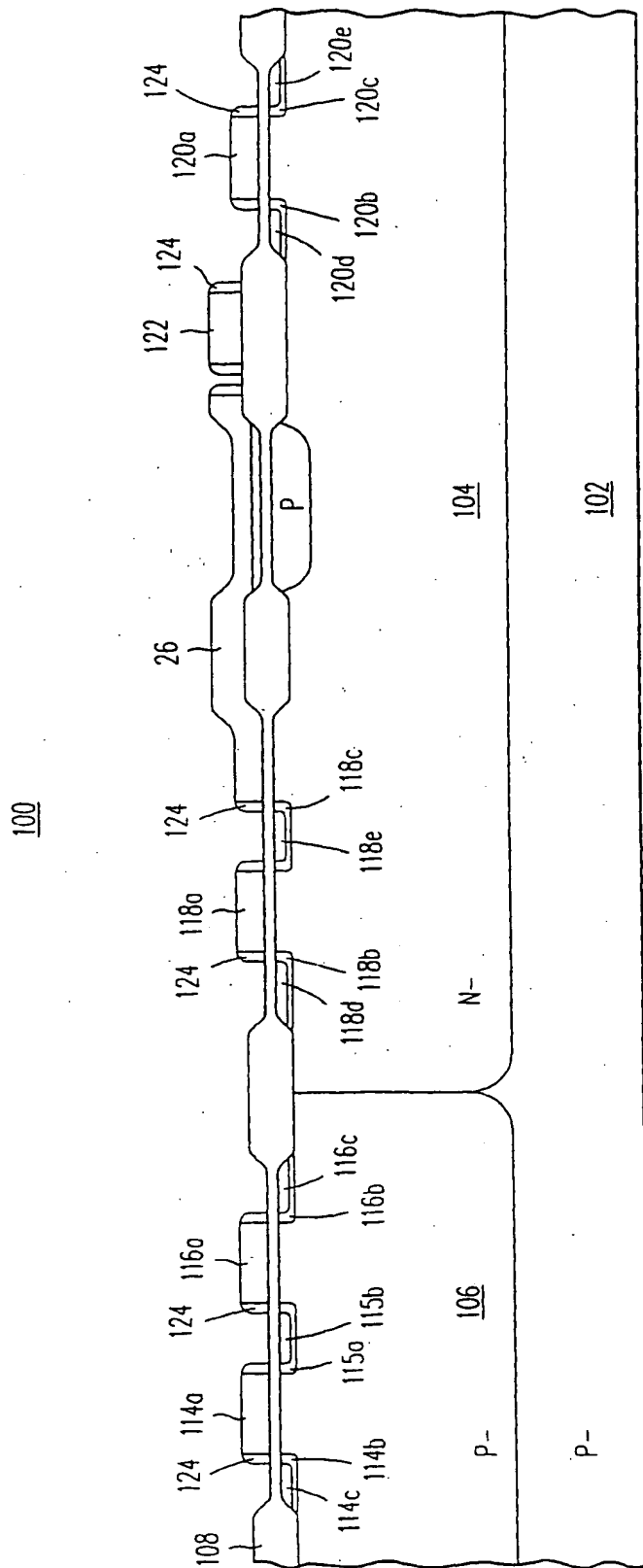


FIG. 14

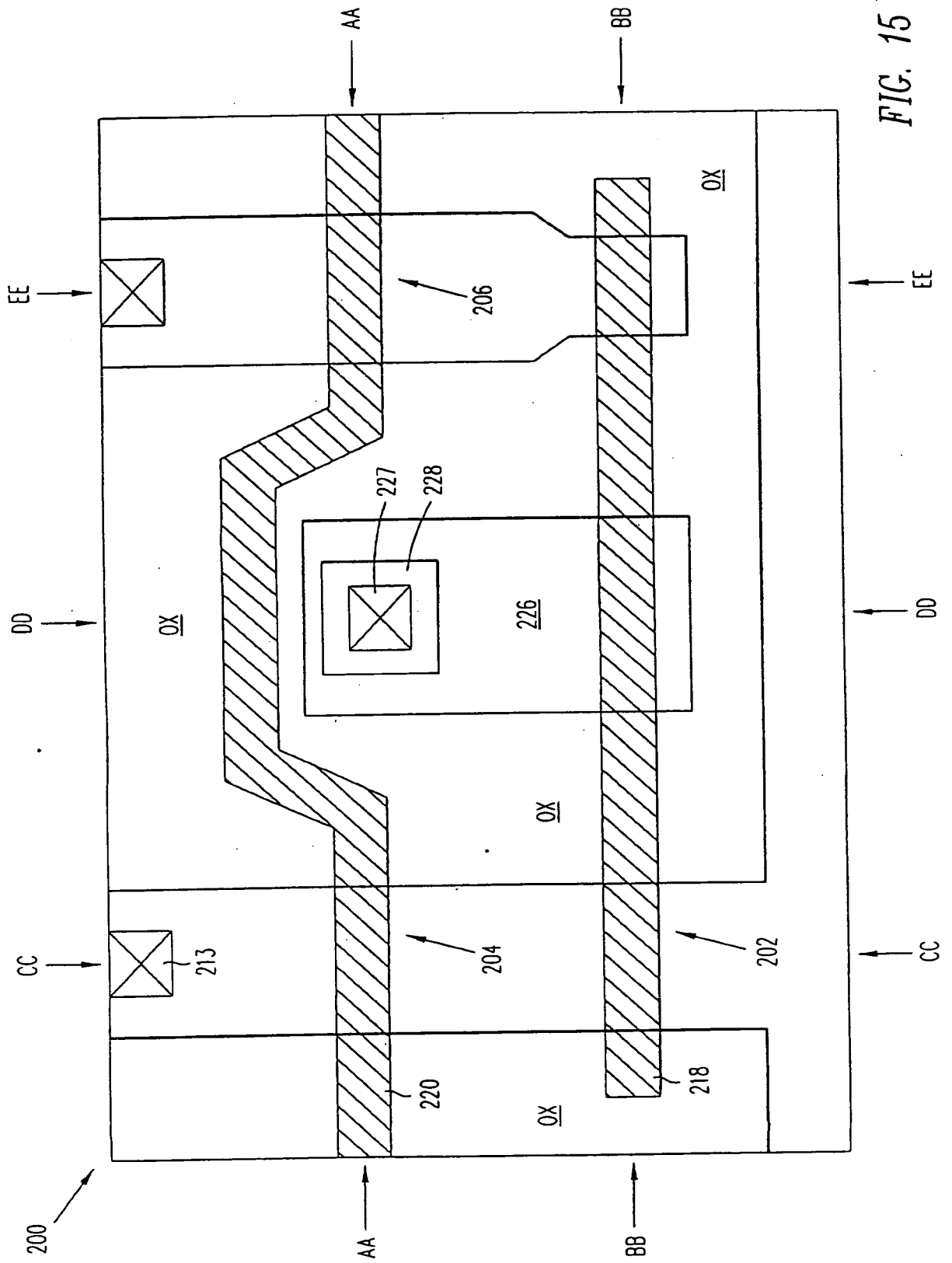


FIG. 15

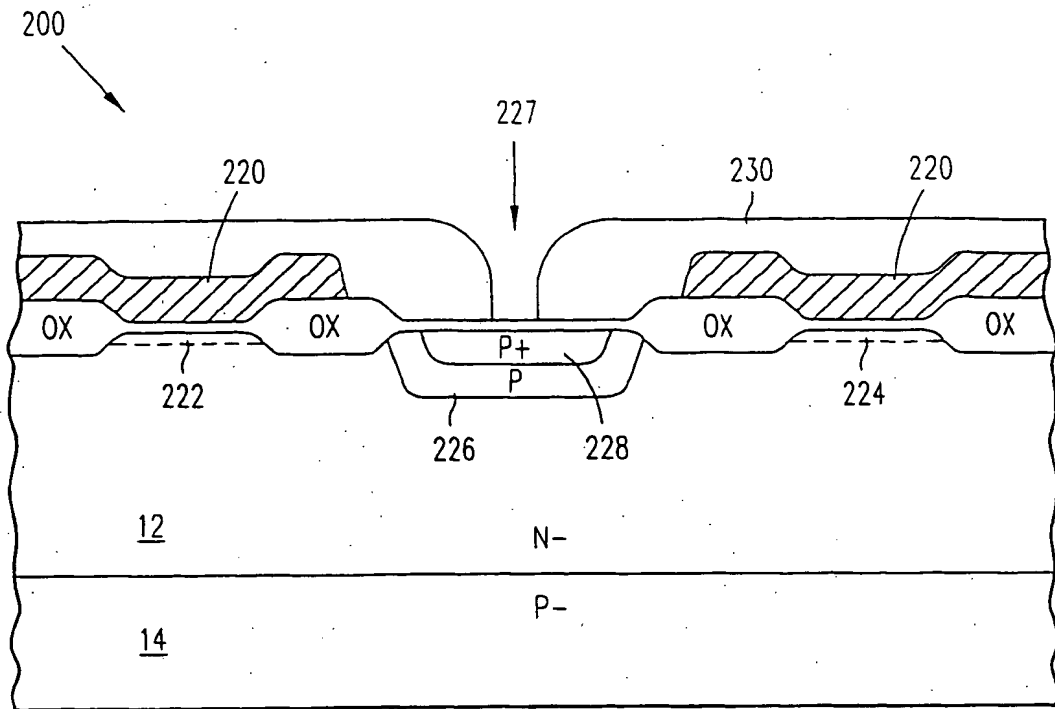


FIG. 16

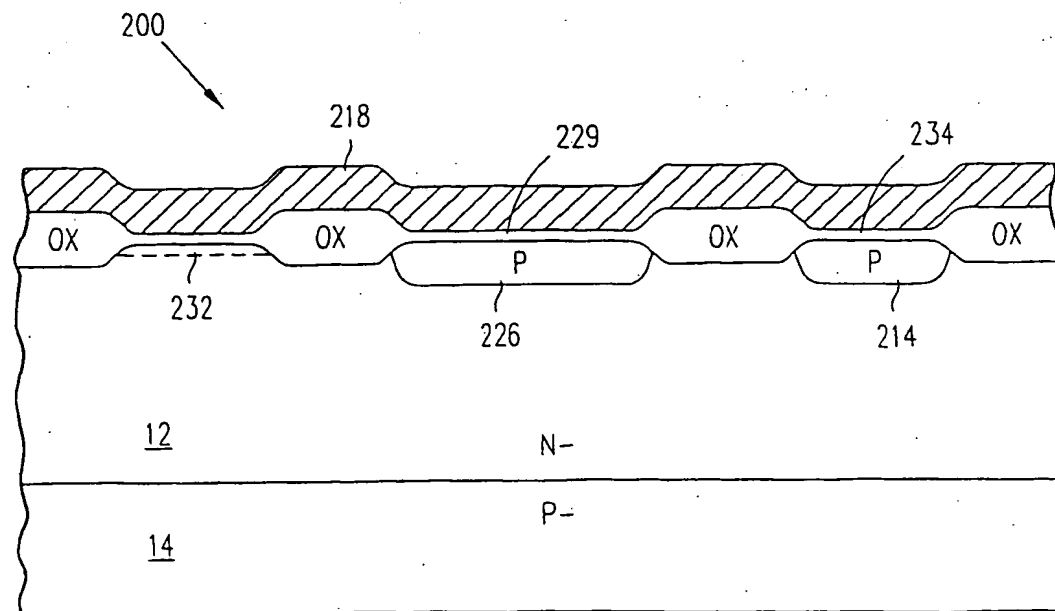


FIG. 17

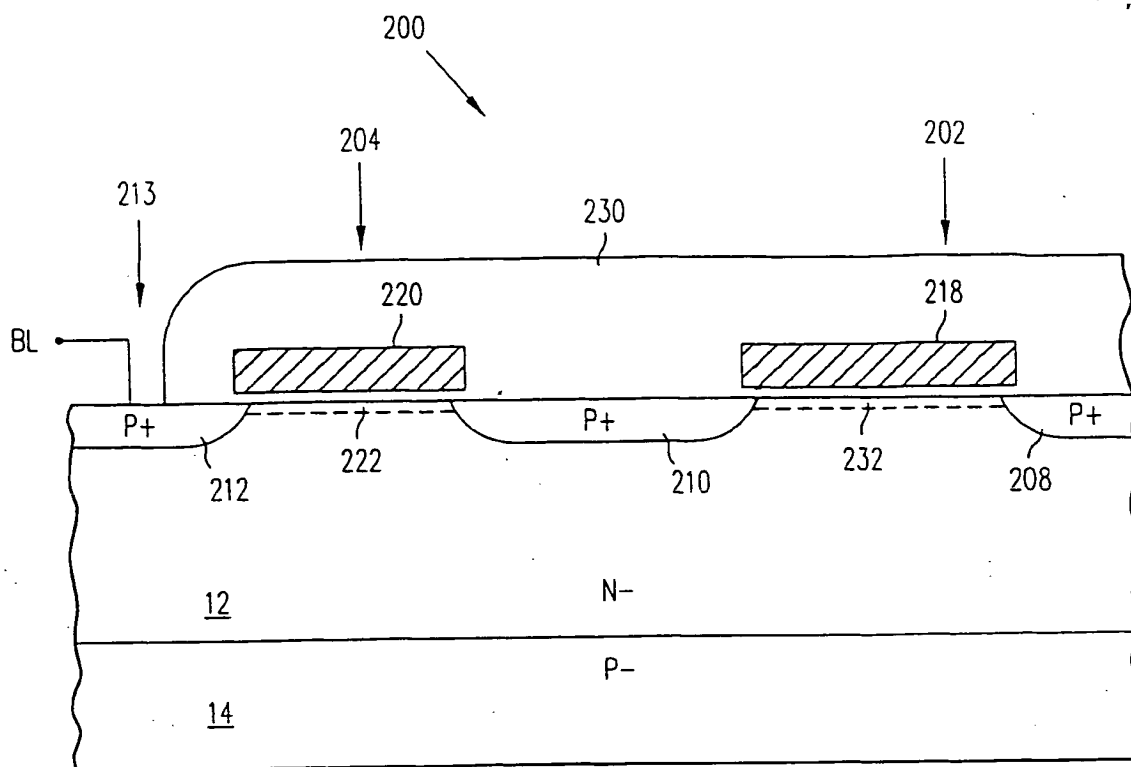


FIG. 18

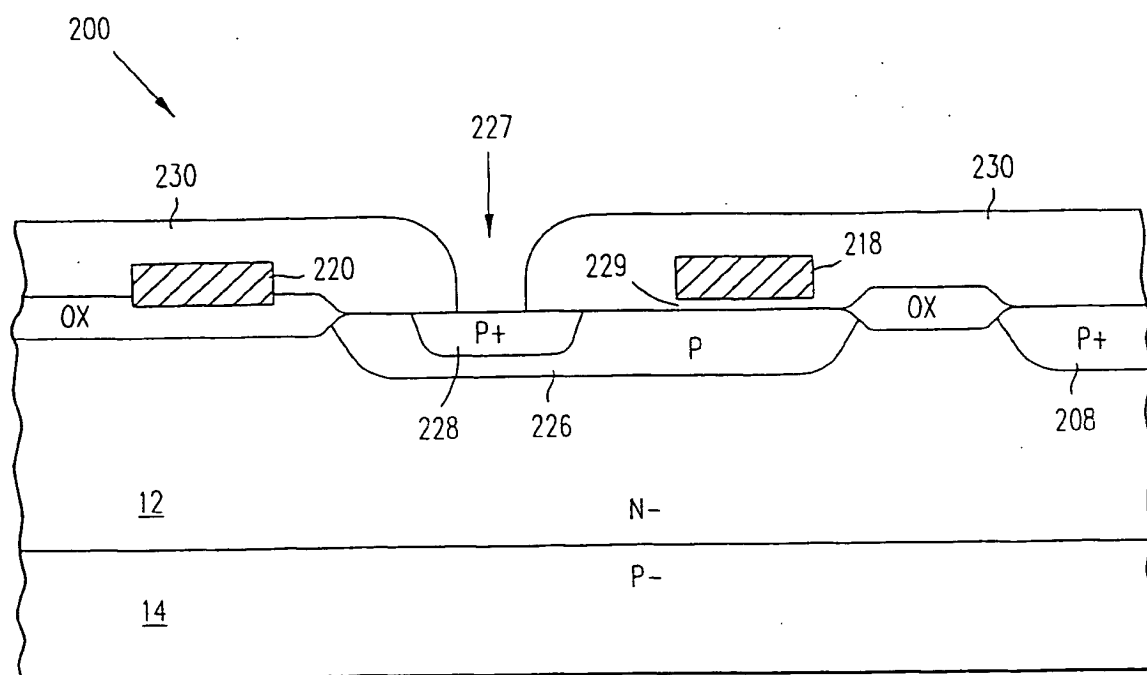


FIG. 19

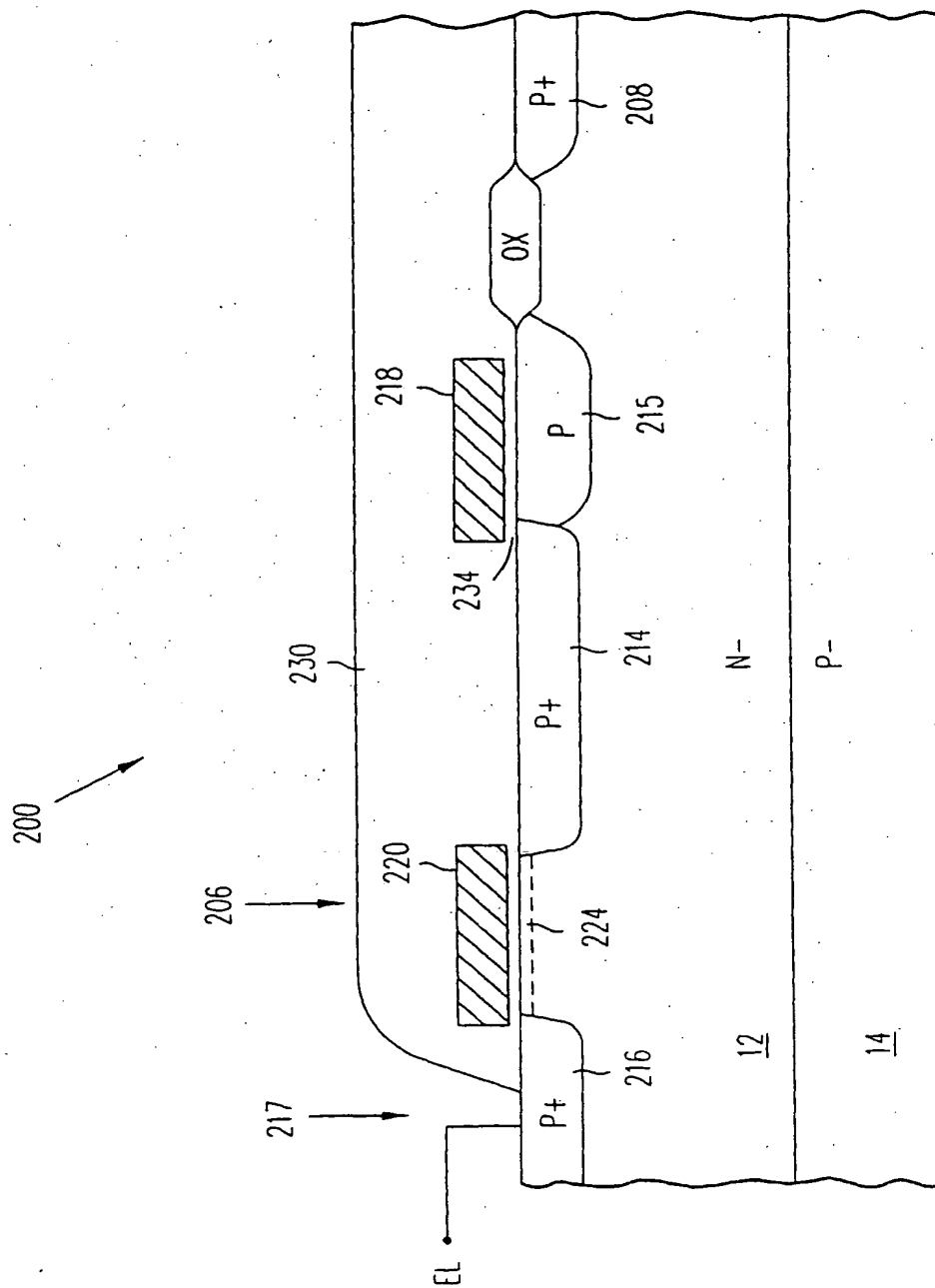


FIG. 20

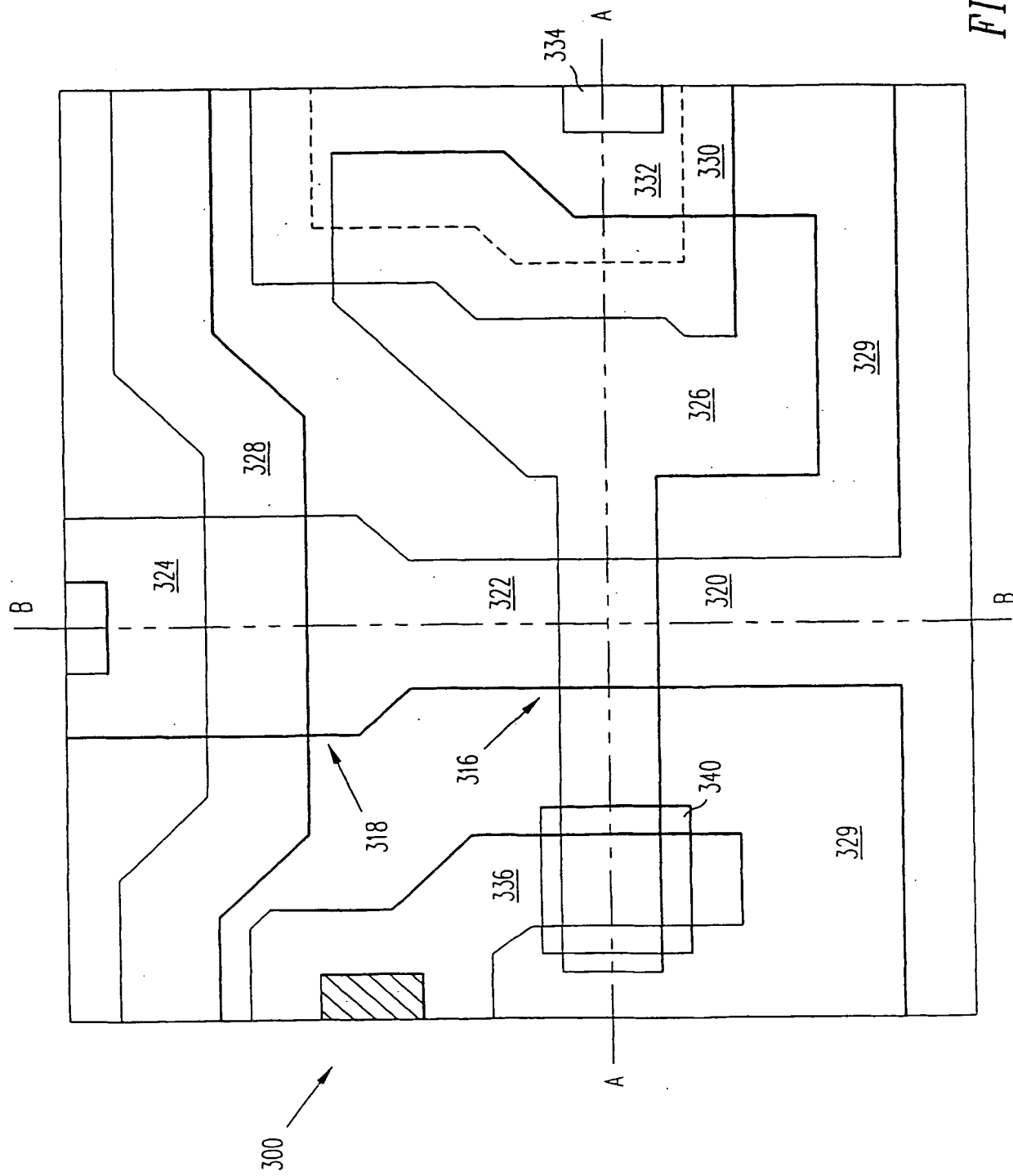


FIG. 21



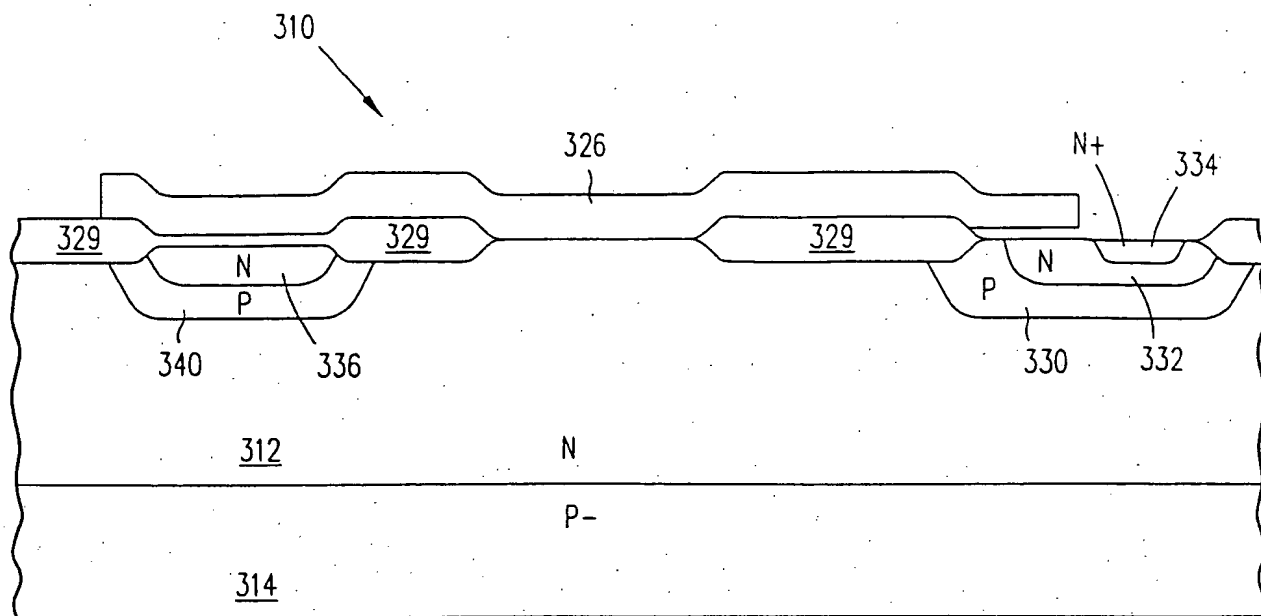


FIG. 22A

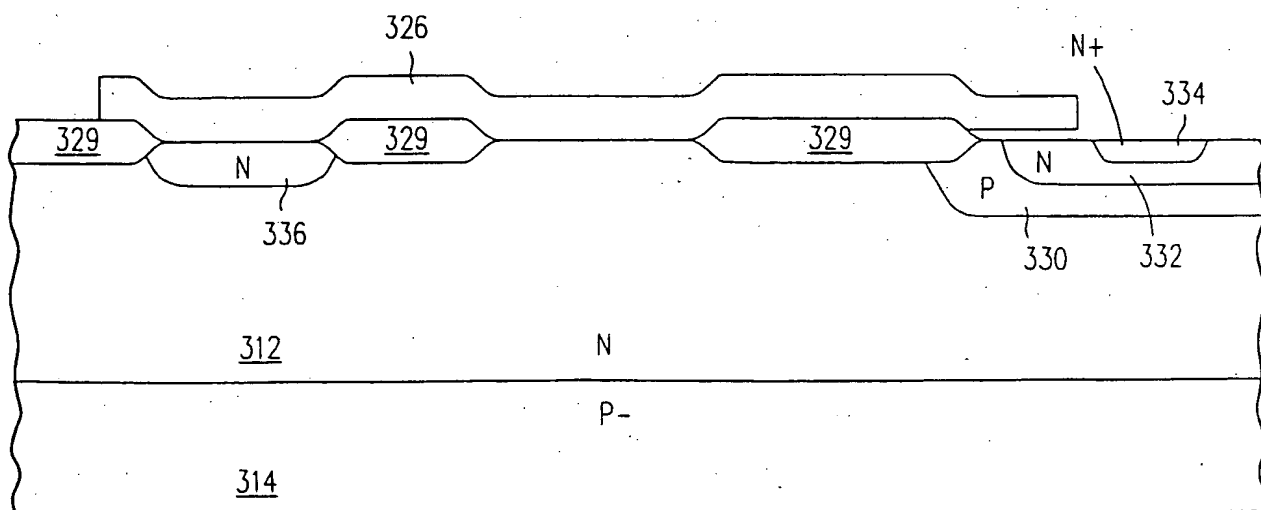


FIG. 22B

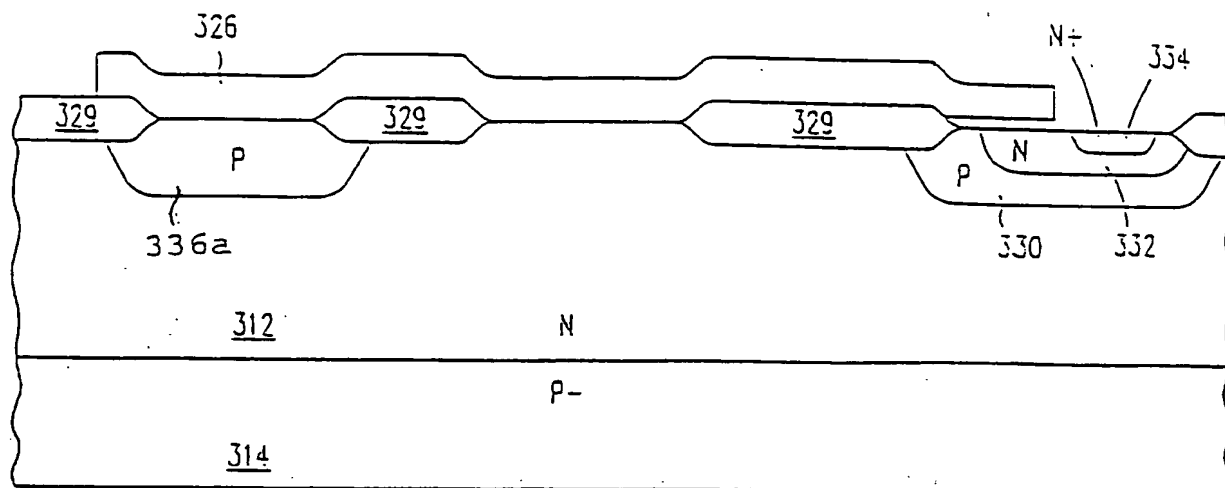


FIG. 22C

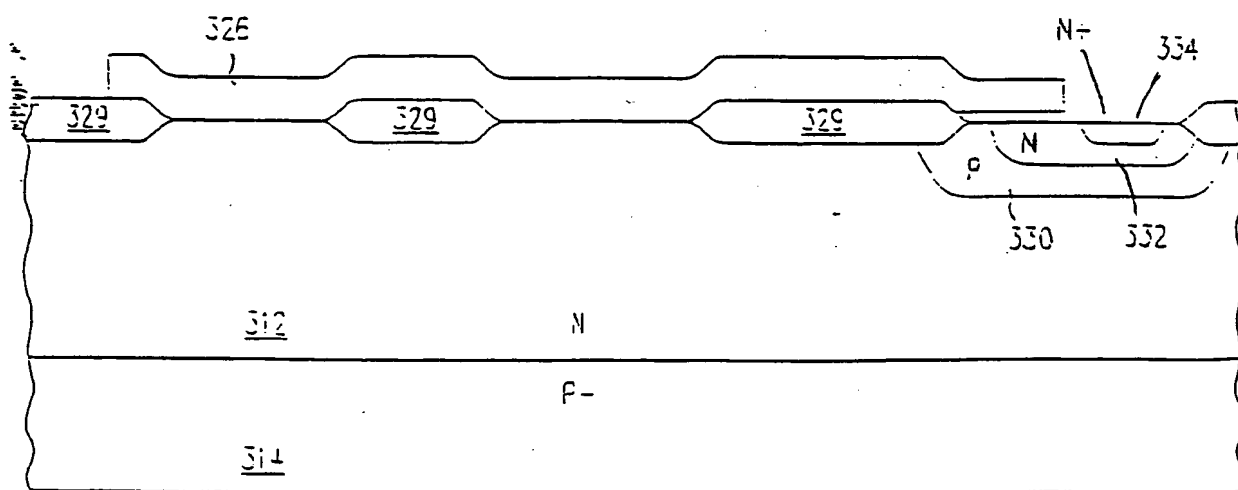


FIG. 22D

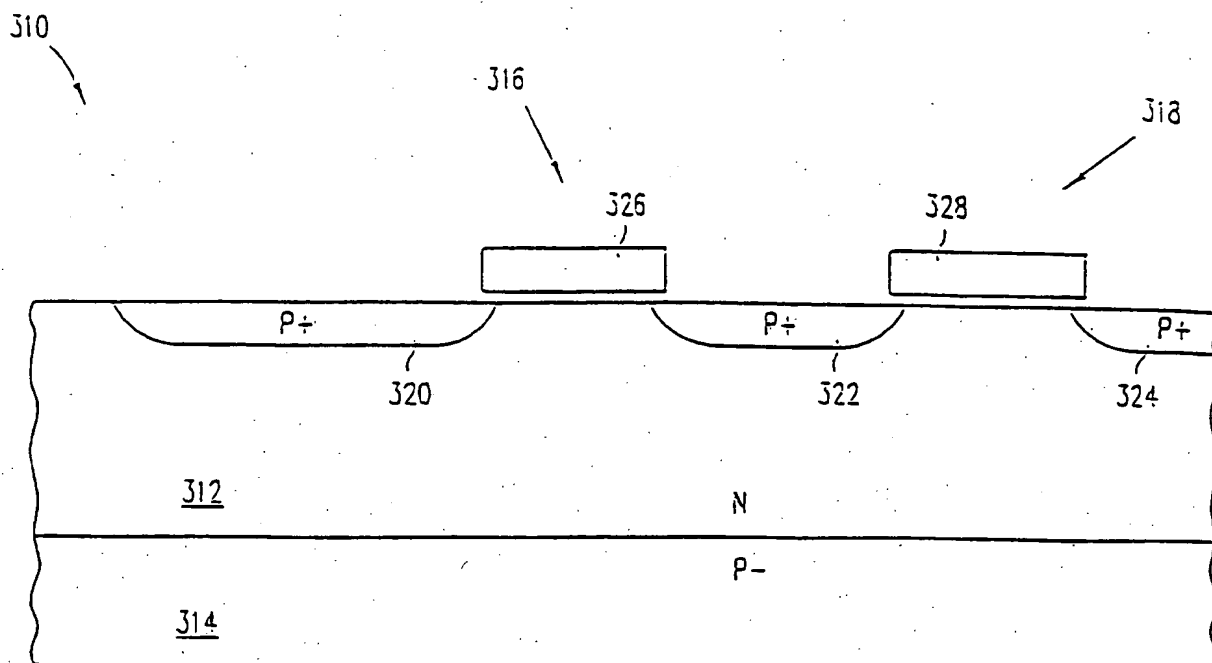


FIG. 23

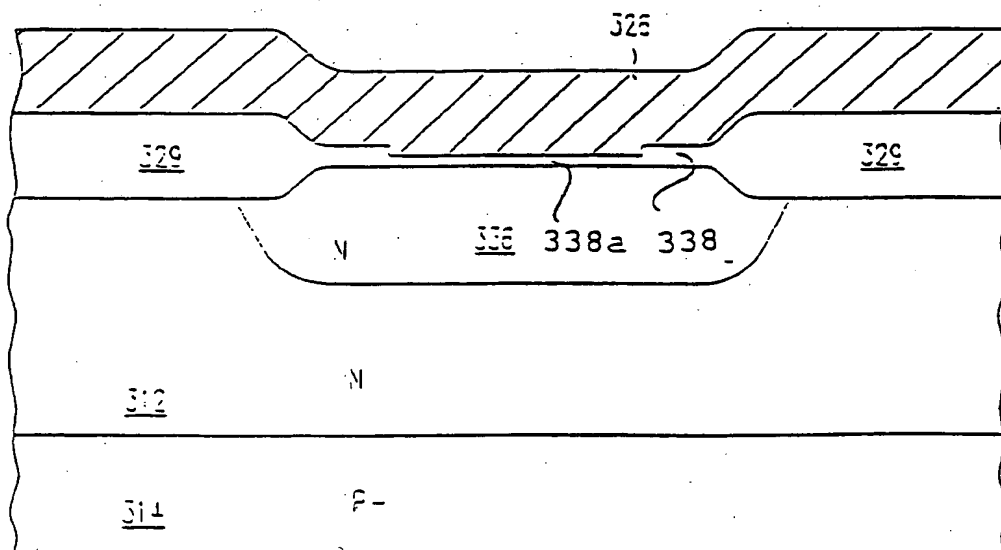


FIG. 24

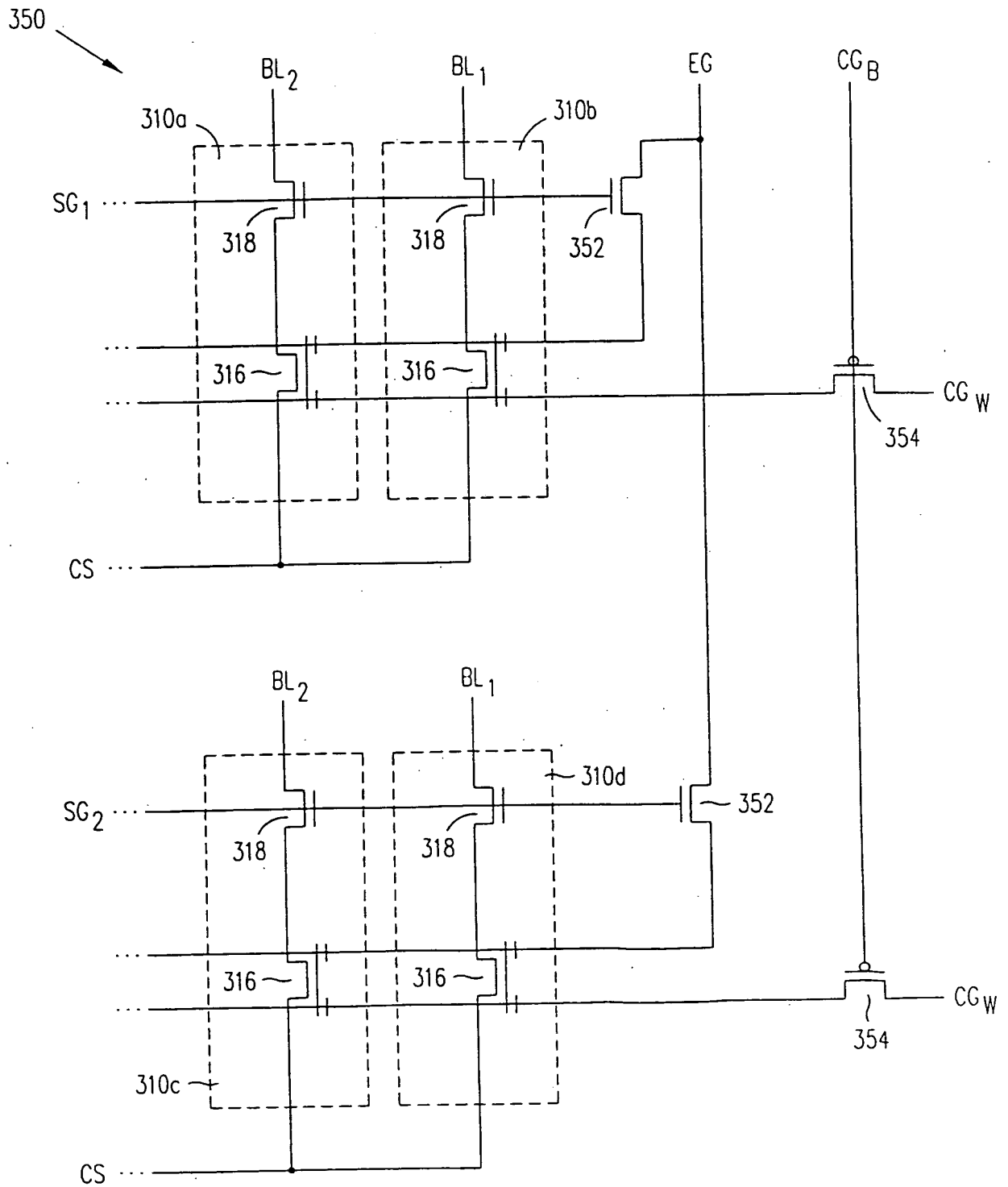


FIG. 25